

# EE 330

## Lecture 34

Layout of Current Mirrors

Common-Centroid Layouts

High Gain Amplifiers

Cascode Amplifiers

# Spring 2024 Exam Schedule

Exam 1      Friday Feb 16

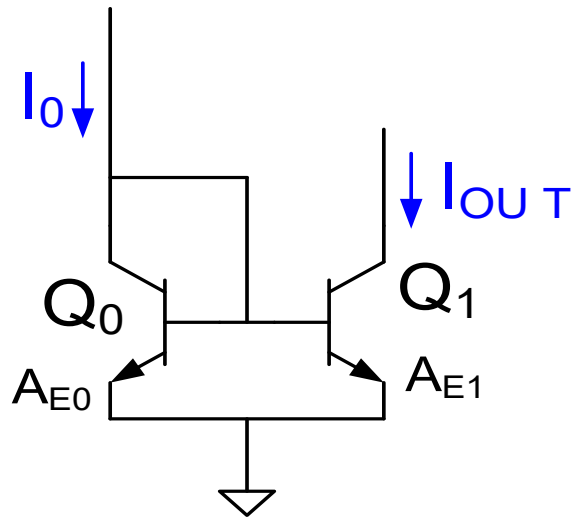
Exam 2      Friday March 8

Exam 3      Friday April 19

Final Exam Tuesday May 7 7:30 AM - 9:30 AM

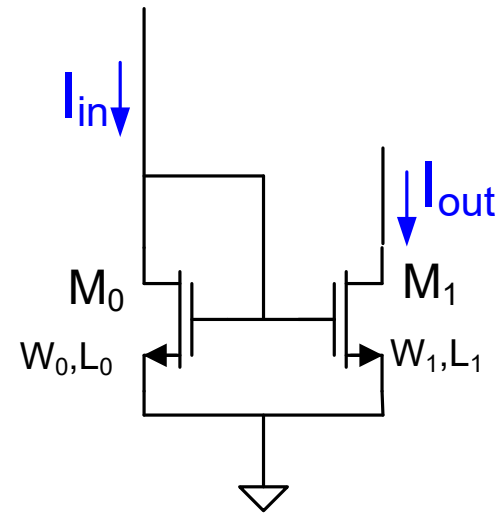


# Current Sources/Mirrors Summary



**npn Current Mirror**

$$I_{out} = \left[ \frac{A_{E1}}{A_{E0}} \right] I_{in}$$

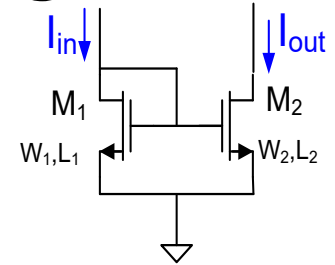


**n-channel Current Mirror**

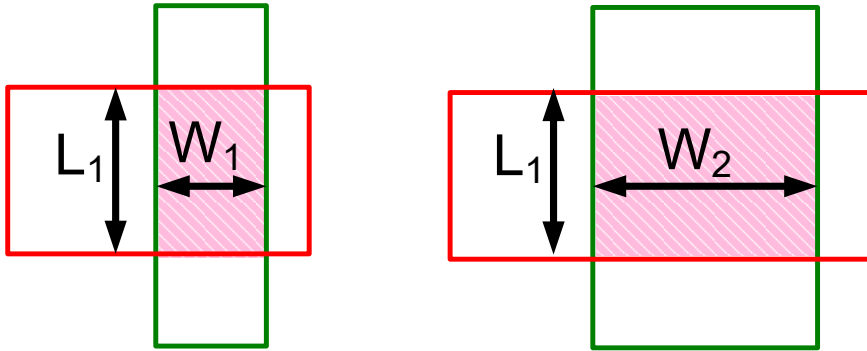
$$I_{out} = \left[ \frac{W_1}{W_0} \frac{L_0}{L_1} \right] I_{in}$$

- Current mirror gain can be accurately controlled !
- Layout is important to get accurate gain (for both MOS and BJT)

# Layout of Current Mirrors

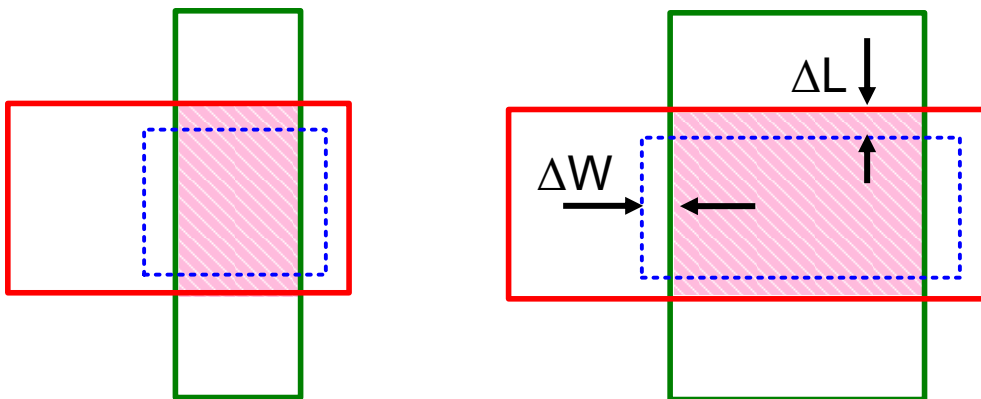


Example with  $M = 2$



Standard layout

$$M = \left[ \frac{W_2}{W_1} \frac{L_1}{L_2} \right]$$



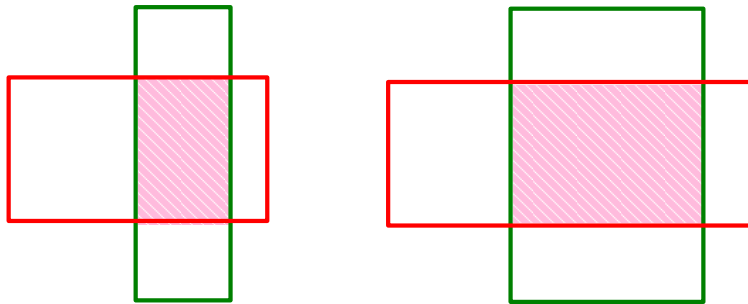
Gate area after fabrication depicted 

$$M = \left[ \frac{W_2 + 2\Delta W}{W_1 + 2\Delta W} \cdot \frac{L_1 + 2\Delta L}{L_2 + 2\Delta L} \right]$$

$$M = \left[ \frac{2W_1 + 2\Delta W}{W_1 + 2\Delta W} \cdot \frac{L_1 + 2\Delta L}{L_1 + 2\Delta L} \right] \neq 2$$

# Layout of Current Mirrors

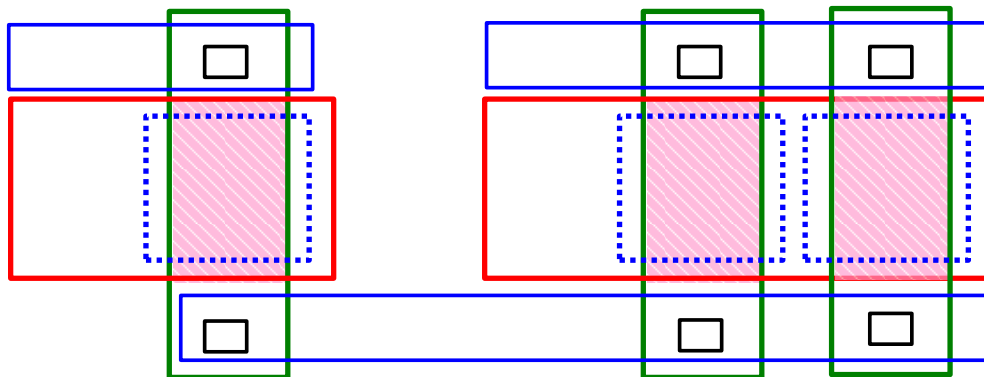
Example with  $M = 2$



Standard layout

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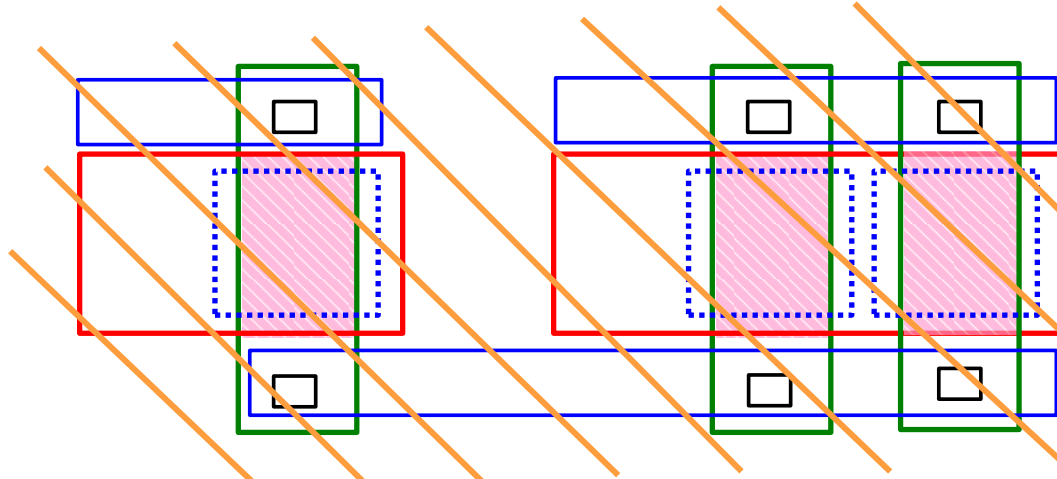


Better Layout

$$M = \left[ \frac{2W_1 + 4\Delta W}{W_1 + 2\Delta W} \cdot \frac{L_1 + 2\Delta L}{L_1 + 2\Delta L} \right] = 2$$

# Layout of Current Mirrors

Example with  $M = 2$



**Better Layout**

Linear Gradient Direction  
of a model parameter  
(e.g.  $\mu$  or  $V_{TH}$ )

$$M = \left[ \frac{2W_1 + 4\Delta W}{W_1 + 2\Delta W} \cdot \frac{L_1 + 2\Delta L}{L_1 + 2\Delta L} \right] = 2$$

But this analysis was based upon assumption of matching of process parameters

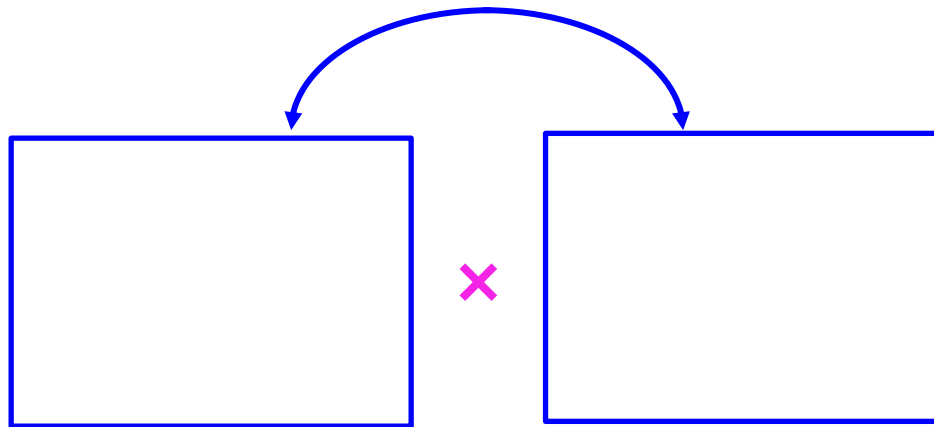
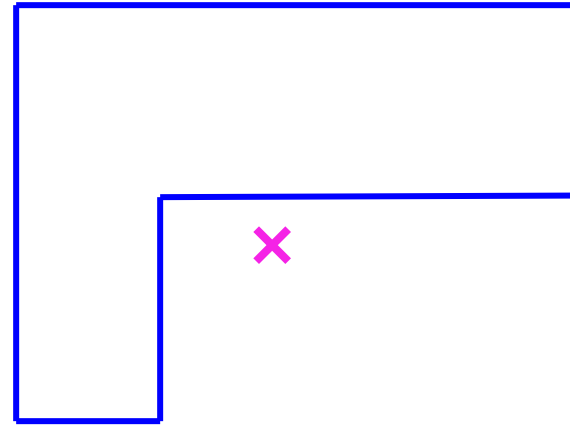
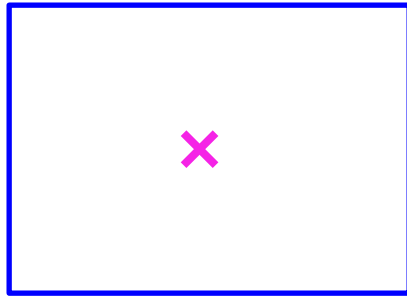
$$\left. \begin{aligned} I_{in} &= \frac{\mu_0 C_{OX} W_0}{2L_0} (V_{GS0} - V_{T0})^2 \\ I_{out} &= \frac{\mu_1 C_{OX} W_1}{2L_1} (V_{GS1} - V_{T1})^2 \end{aligned} \right\}$$

Even with this better layout, the current ratio will not be 2 if gradient effects such as those depicted here are shown

And both magnitude and direction of gradient effects are a random variable which will vary across a die

# Centroid and Common Centroid

✕ Denotes Geometric Centroid

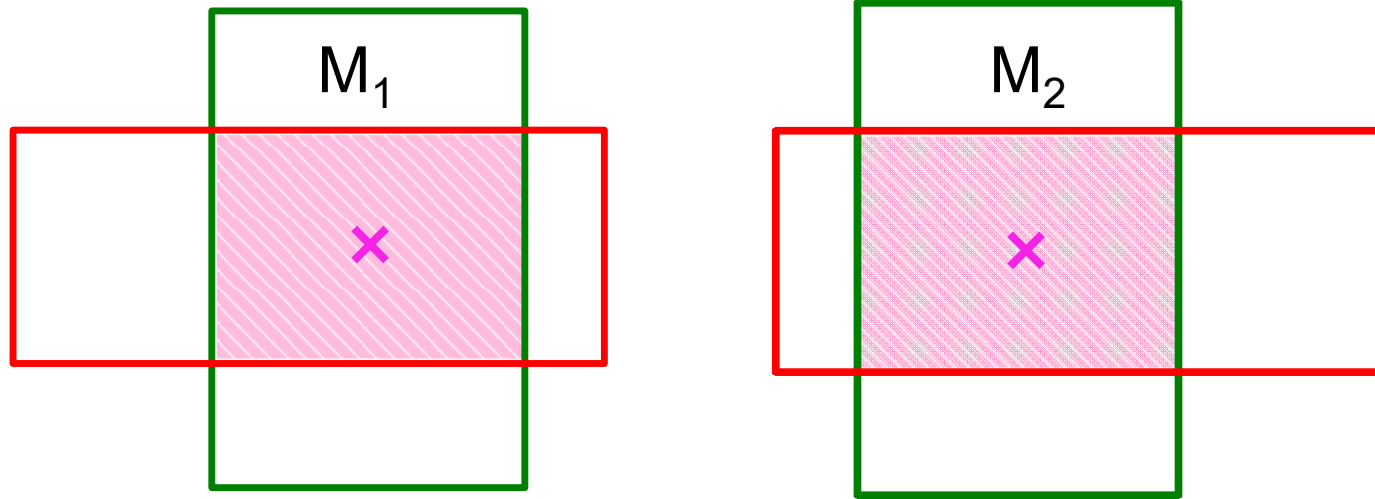




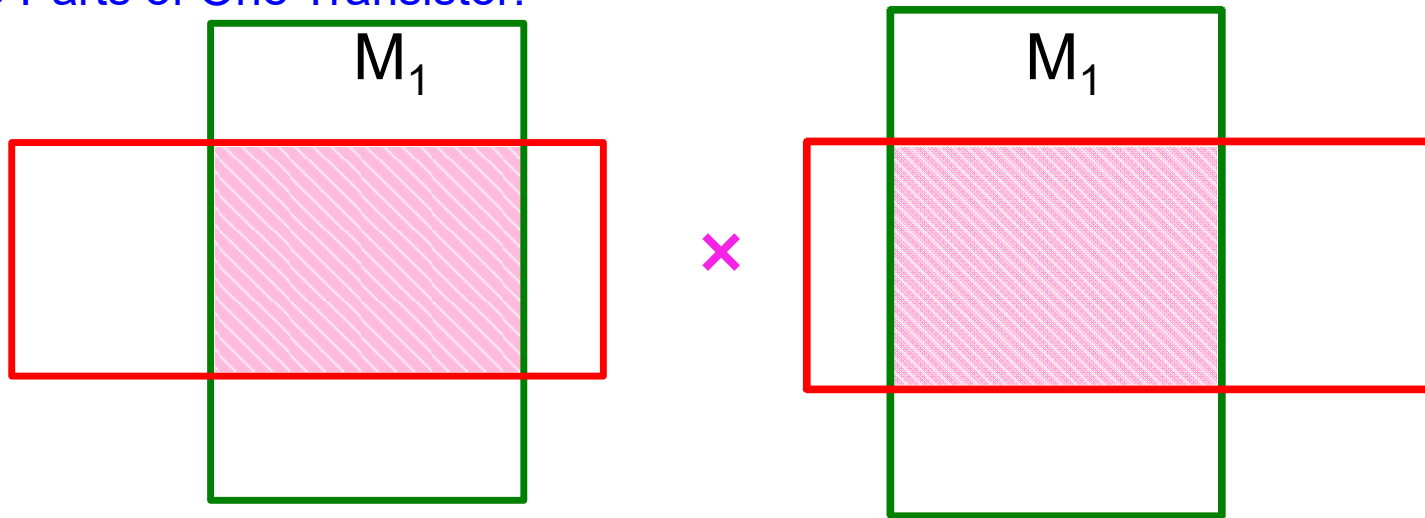
# Centroid and Common Centroid

Geometric Centroids of Channel

Two Transistors:

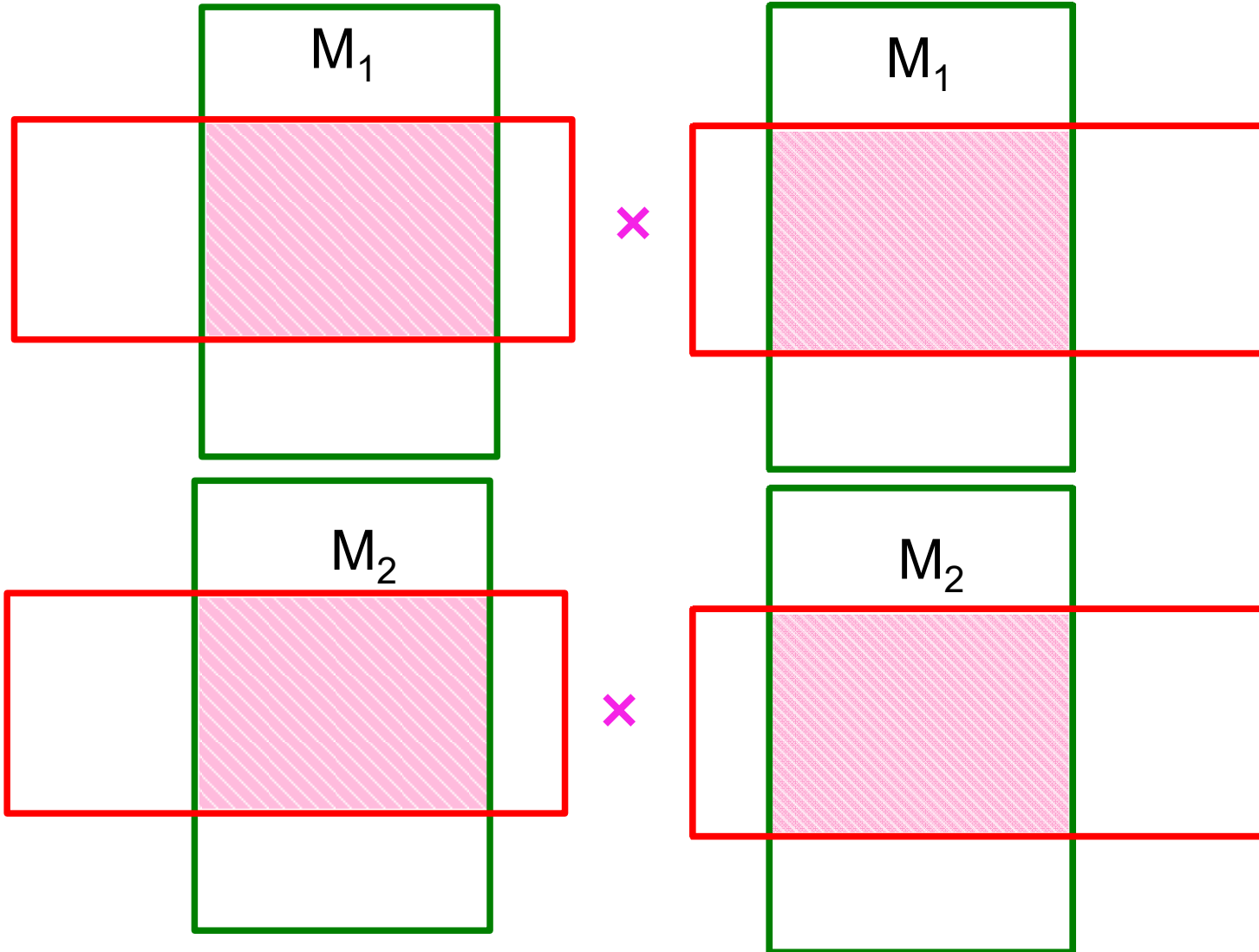


Two Parts of One Transistor:



# Centroid and Common Centroid

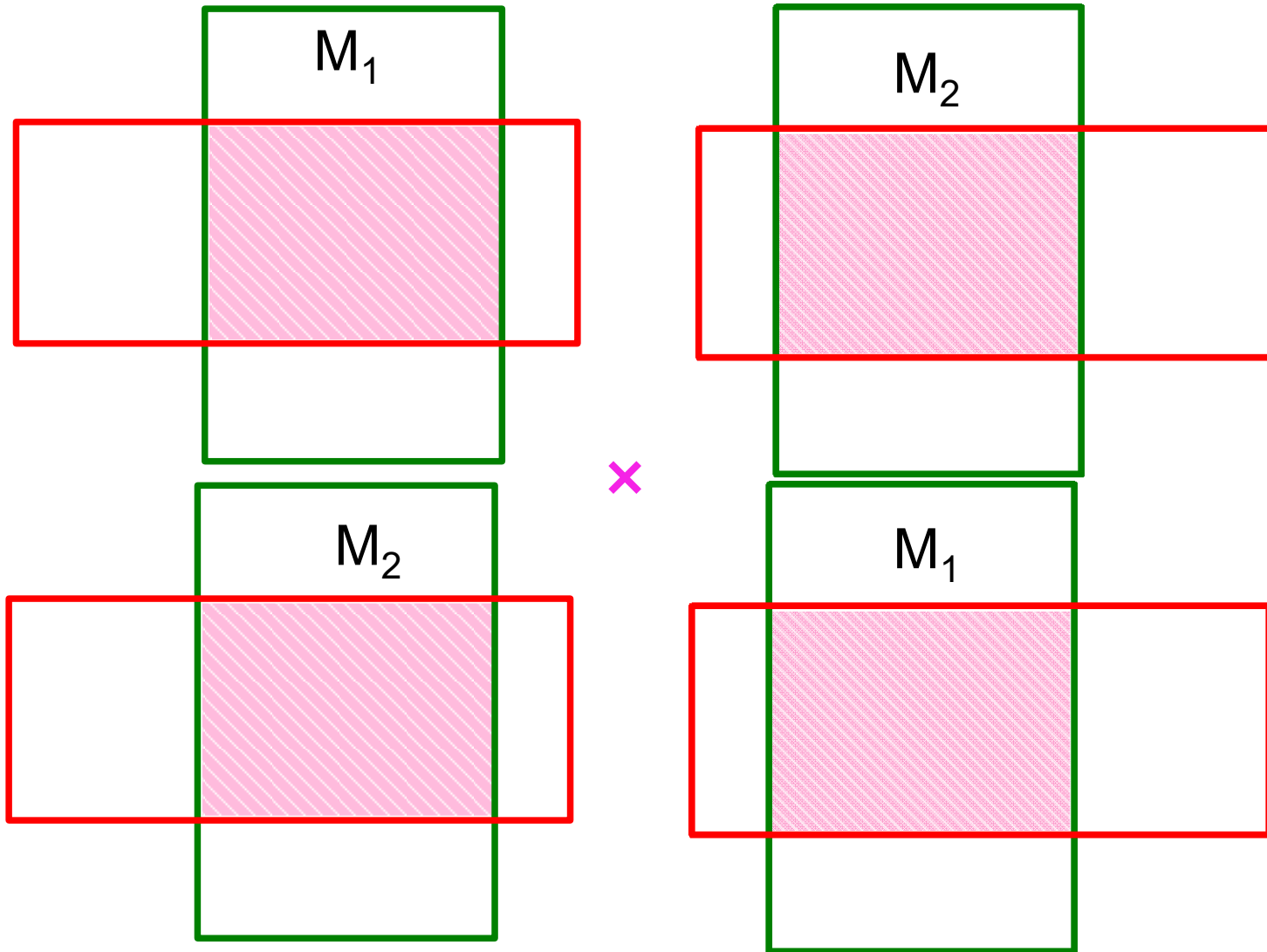
Two Transistors each with two parts:



# Centroid and Common Centroid

Common Centroid for Ideally Matched Devices

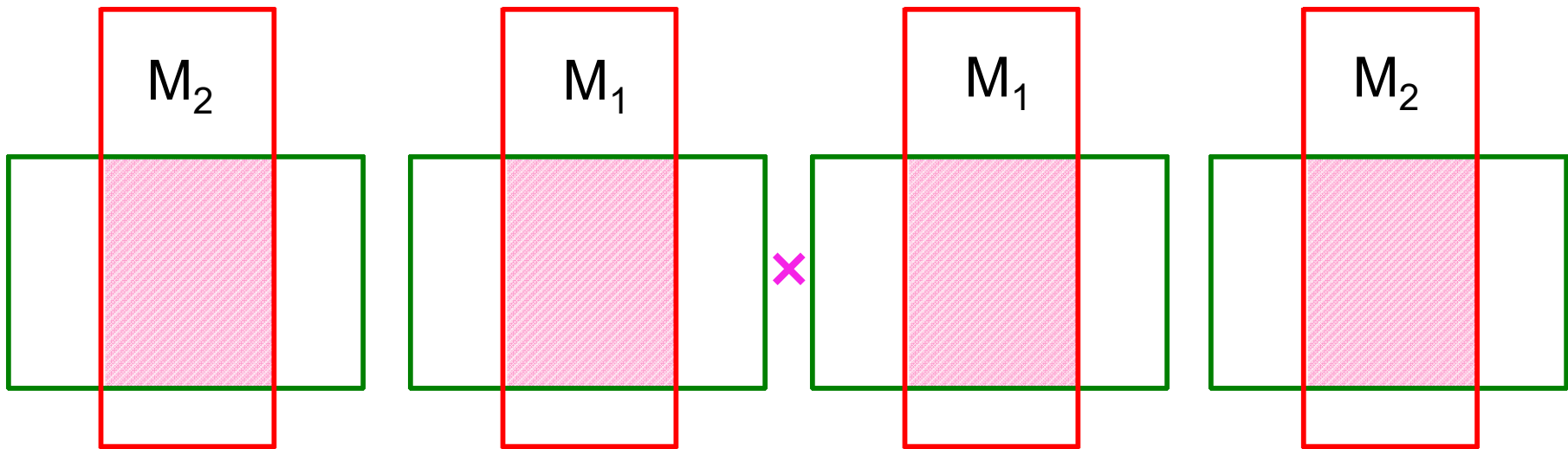
Two Transistors each with two parts:



# Centroid and Common Centroid

Common Centroid for Matched Devices

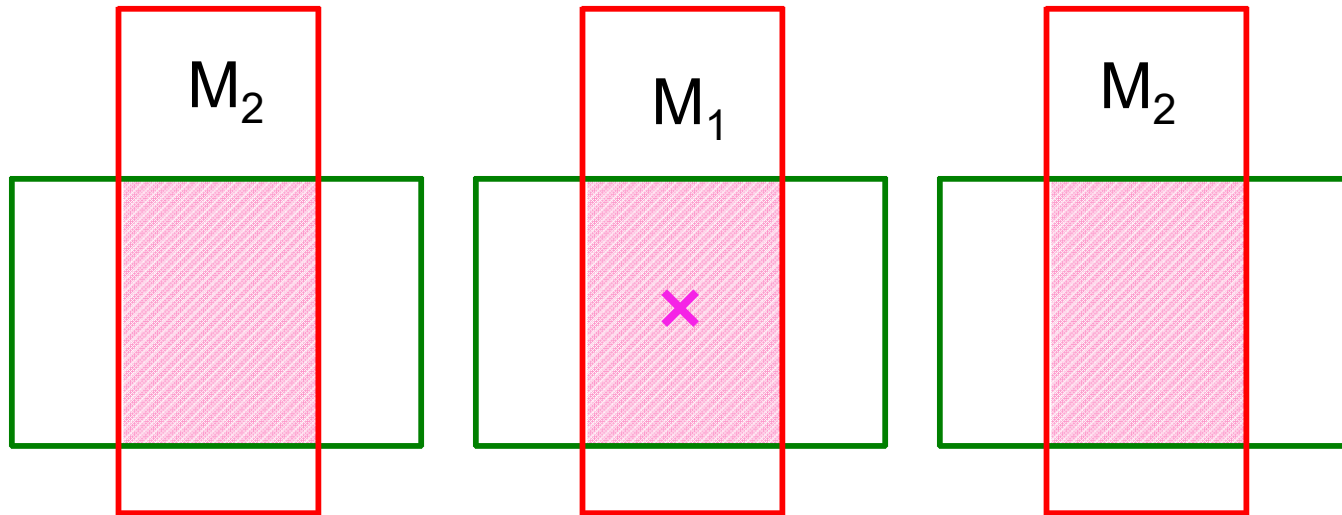
Two Transistors each with two parts:



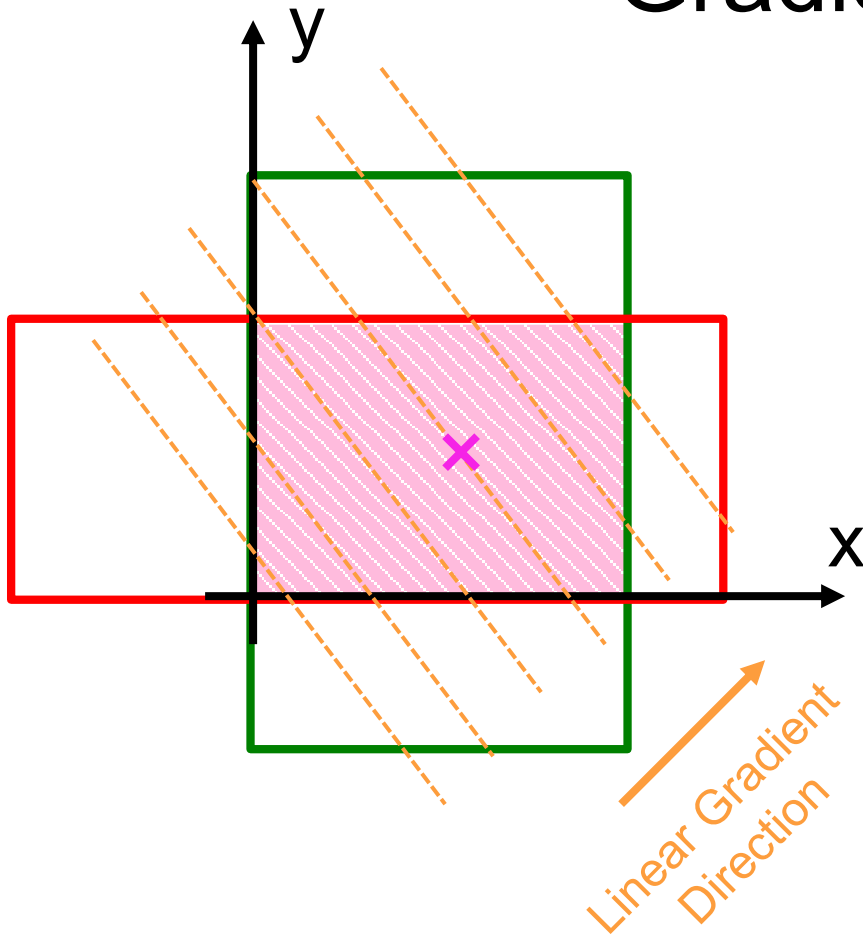
# Centroid and Common Centroid

Common Centroid for Ratioed Devices  $M = \frac{W_2 L_1}{W_1 L_2} = 2$

Two Transistors with different effective widths:



# Gradient



Threshold voltage  
dependent upon position

$$V_{TH}(x,y)$$

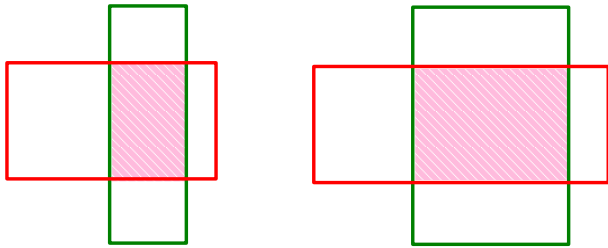
- Significant changes in threshold voltage can occur due to gradient effects
- This can seriously degrade matching in matching-critical circuits

- If the threshold voltage of a transistor changes with position, it can be reasonably accurately modeled with an “equivalent” threshold voltage
- For linear gradient,  $V_{THEQ} = V_{TH}(X_C, Y_C)$

$$\times : (X_C, Y_C)$$

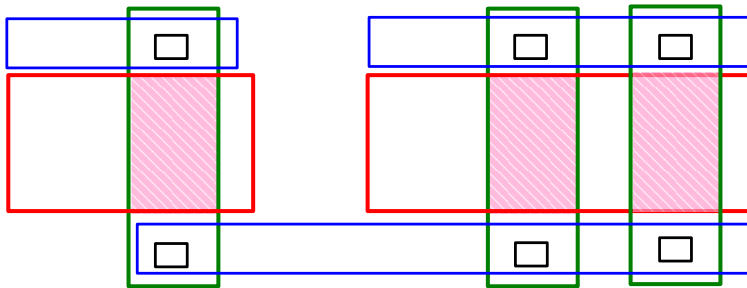
# Layout of Current Mirrors

Example with  $M = 2$



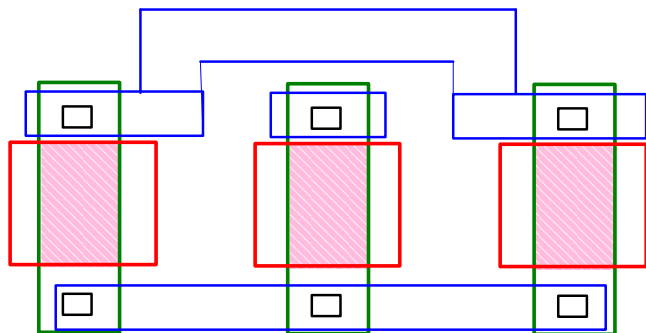
Standard layout

$$M = \left[ \frac{W_2 L_1}{W_1 L_2} \right]$$



Better Layout

$$M = \left[ \frac{2W_1 + 4\Delta W}{W_1 + 2\Delta W} \cdot \frac{L_1 + 2\Delta L}{L_1 + 2\Delta L} \right] = 2$$

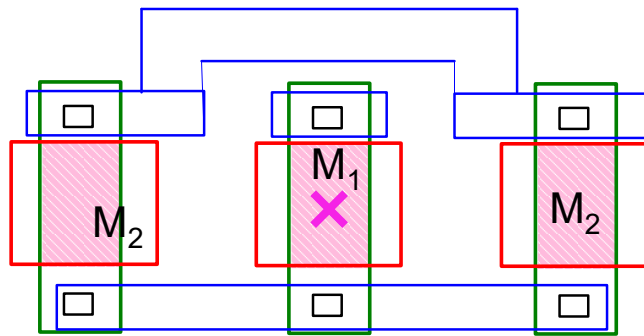


Even Better Layout

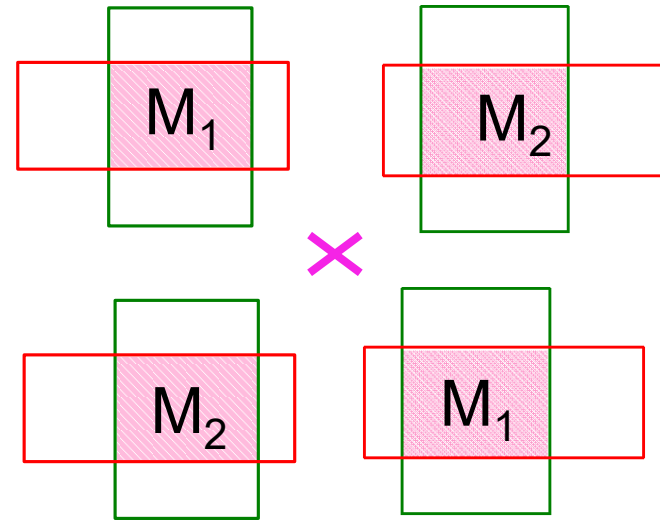
$$M = \left[ \frac{2W_1 + 4\Delta W}{W_1 + 2\Delta W} \cdot \frac{L_1 + 2\Delta L}{L_1 + 2\Delta L} \right] = 2$$

- This is termed a common-centroid layout
- Linear gradient mismatch eliminated with common-centroid layout !

# Common-Centroid Layouts



$$M = \left[ \frac{2W_1}{W_1} \cdot \frac{L_1}{L_1} \right] = 2$$

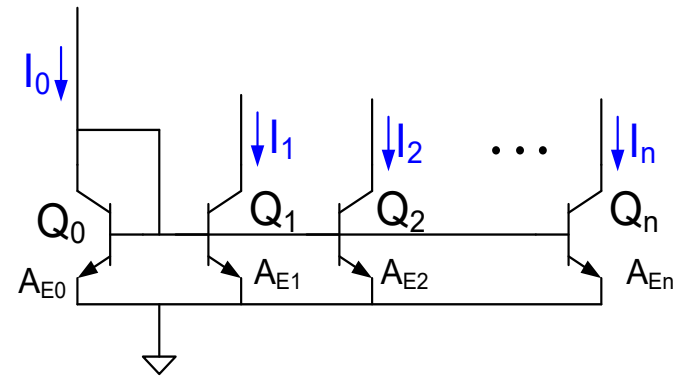
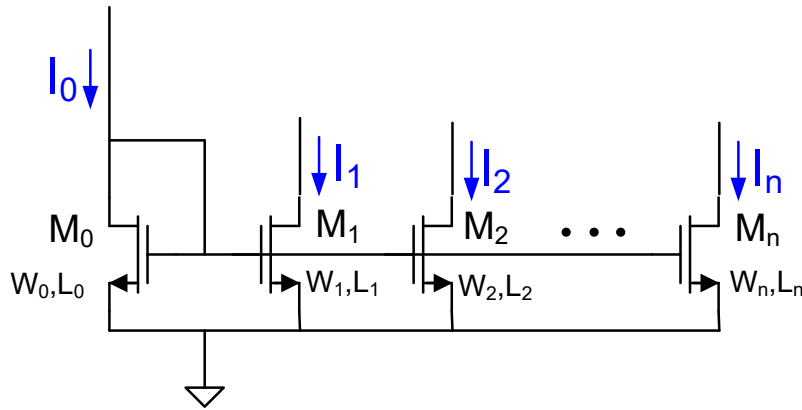


$$M = \left[ \frac{2W_1}{2W_1} \cdot \frac{L_1}{L_1} \right] = 1$$

- Individual transistors often decomposed into parallel multiple unary devices connected in parallel
- Common-Centroid layout approach widely used to minimize (ideally cancel) gradient effects in matching-critical circuits
- Applications extend well beyond current mirrors
- More than 2 devices can share a common centroid



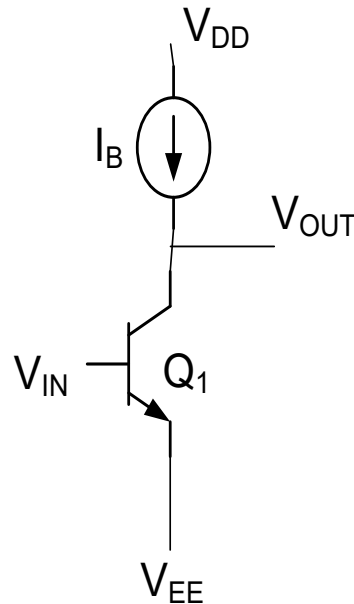
# Current Sources/Mirrors



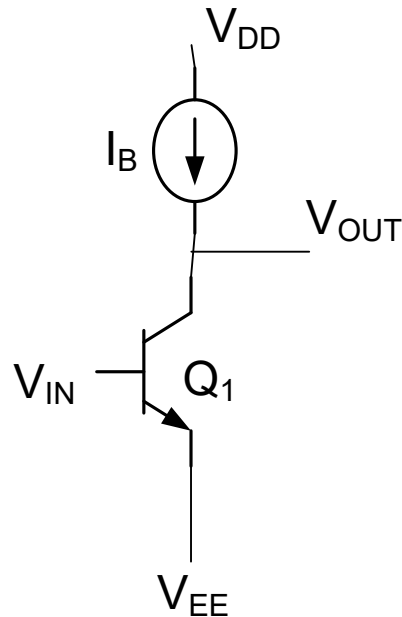
If  $I_0$  is practically generated (it can be), now have available a large number of accurate current sources or sinks that can be used for biasing and for other purposes on chip !

# High-gain amplifier

Will now return to discussion of high gain amplifiers



# High-gain amplifier

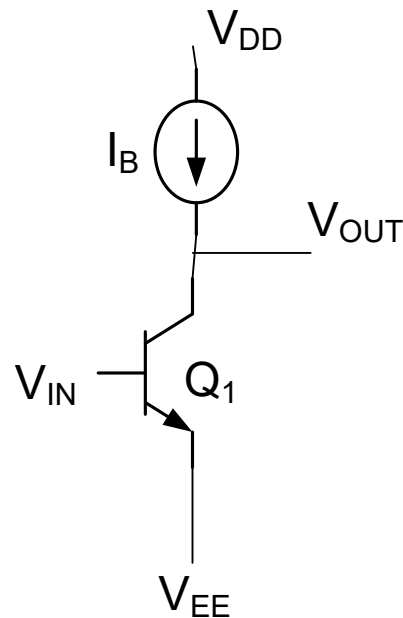


$$A_V \cong -8000$$

## Why are we interested in high-gain amplifiers?

- High gain amplifiers typically have some very undesirable properties  
Nonlinear, gain highly dependent upon process variations and temperature, frequency response poor, noisy, ....
- So we can build feedback amplifiers !!

# High-gain amplifier



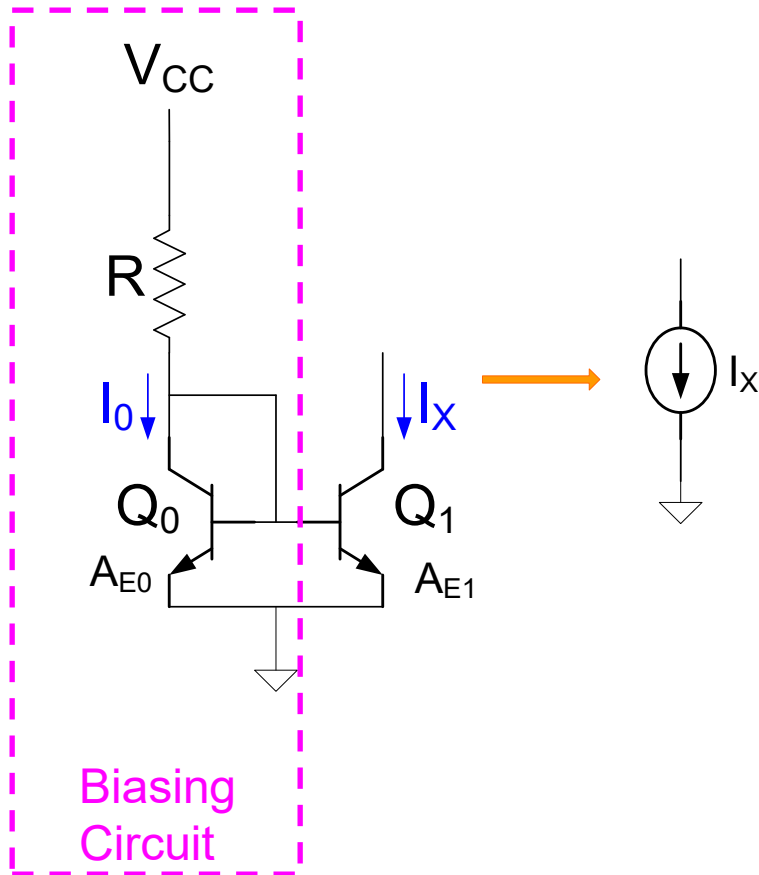
$$A_V \cong -8000$$

→ How can we build the current source?

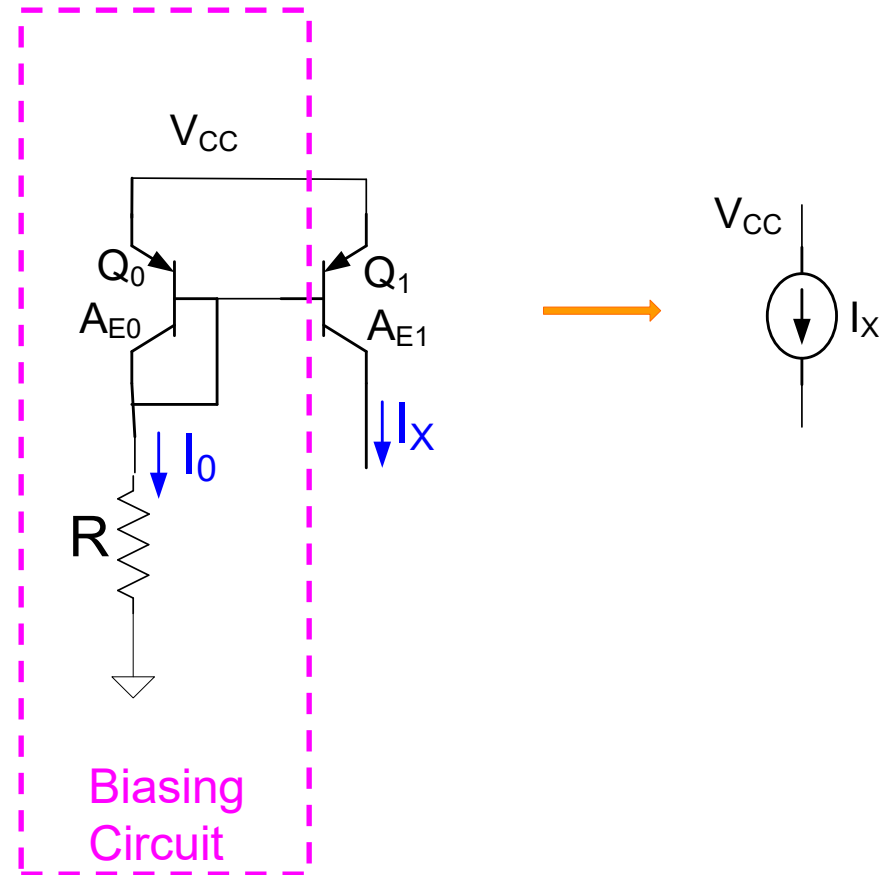
What is the small-signal model of an actual current source?

# Basic Current Sources and Sinks

## Bipolar Mirror-Based Current Sink

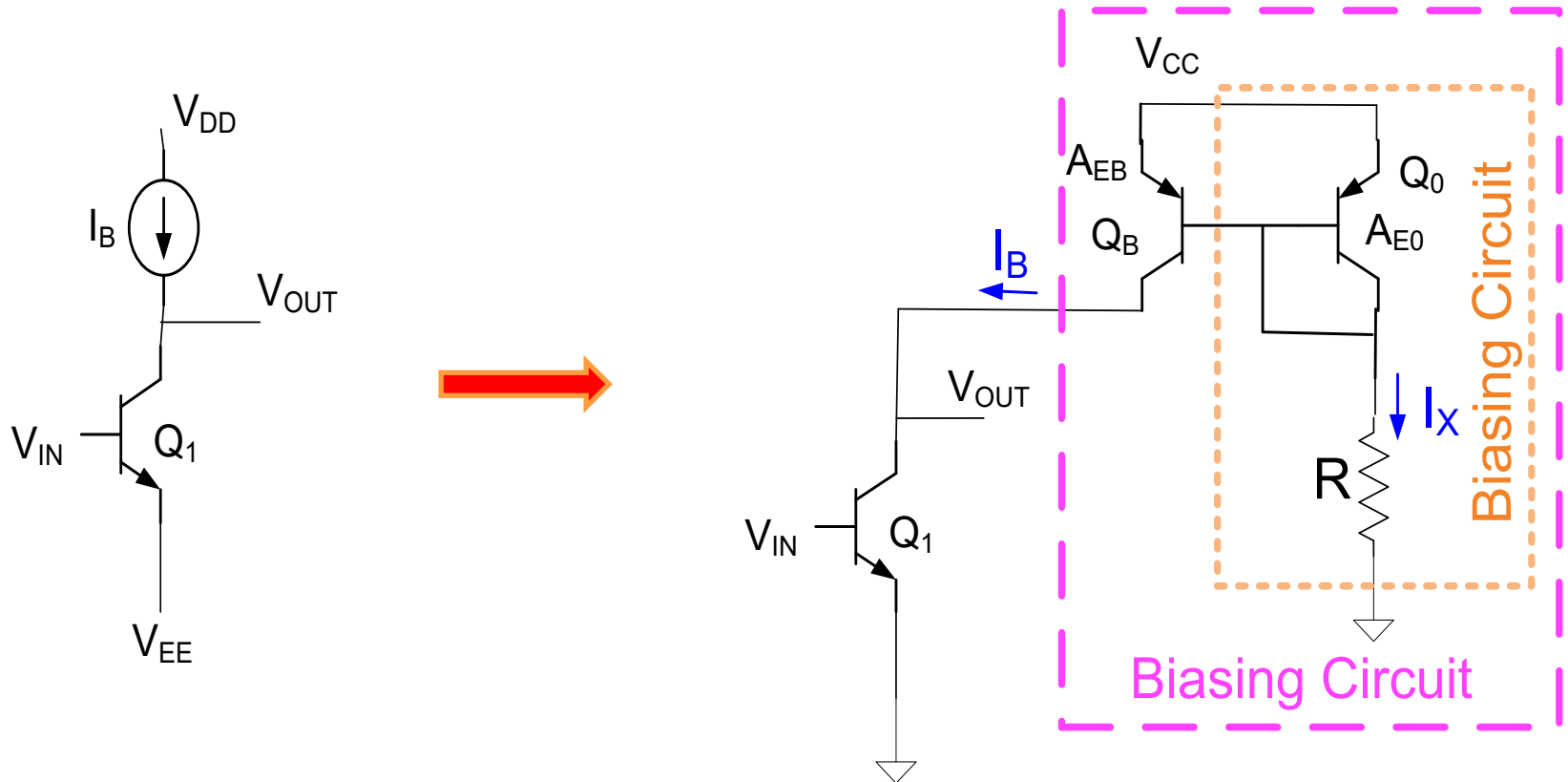


## Bipolar Mirror-Based Current Source



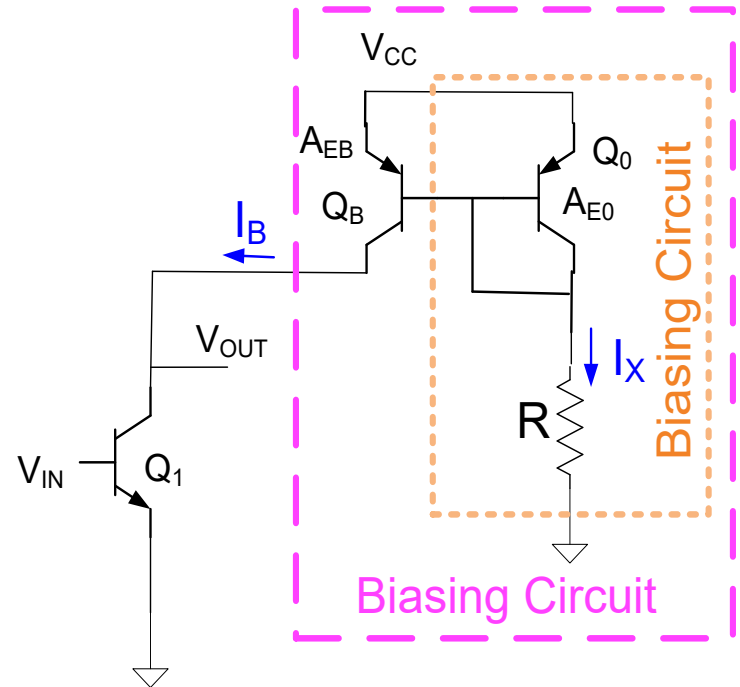
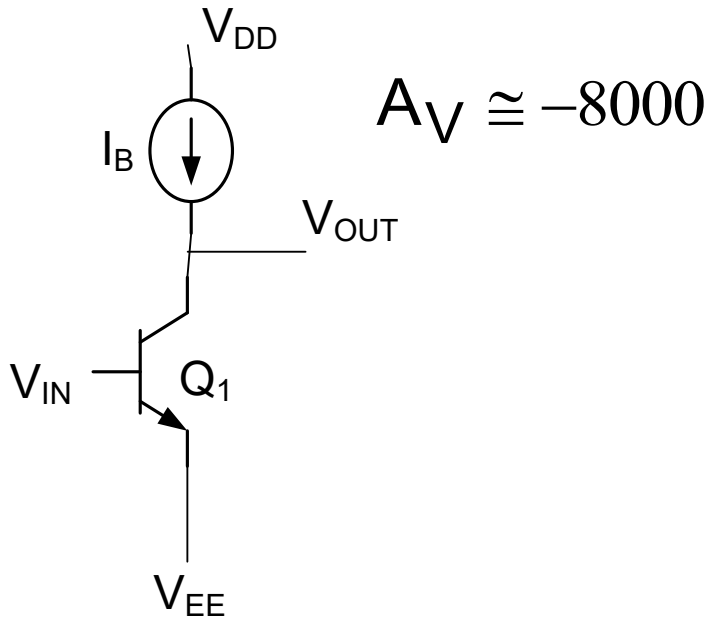
Biassing circuit uses same  $V_{CC}$  as amplifier and no other independent sources

# High-gain amplifier



- Bias circuitry requires only a single independent dc voltage source, resistor, and BJT !
- Incremental overhead is only one transistor,  $Q_B$

# High-gain amplifier



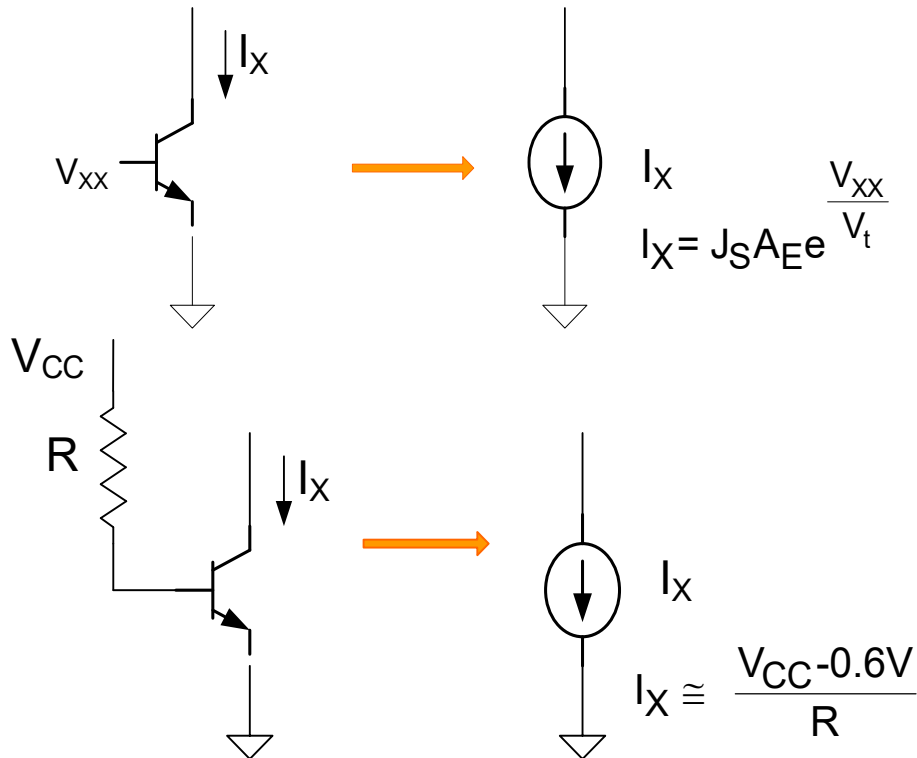
How can we build the current source?

→ What is the small-signal model of an actual current source?

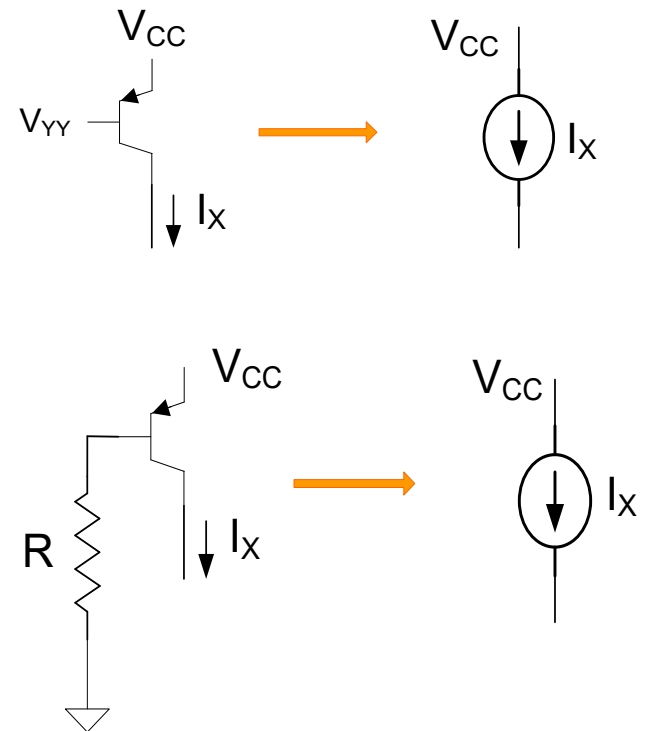
# Basic Current Sources and Sinks

What is the small-signal model of an actual current source?

## Basic Bipolar Current Sinks



## Basic Bipolar Current Sources

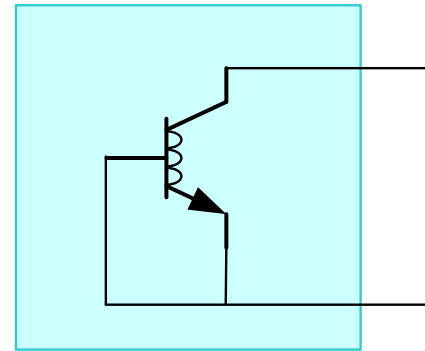
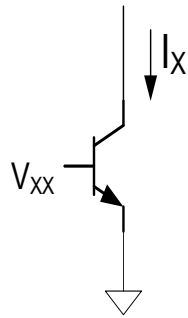


- Very practical methods for biasing the BJTs (or MOSFETs) can be used
- Current Mirrors often used for generating sourcing and sinking currents
- Can think of biasing transistors with  $V_{XX}$  and  $V_{YY}$  in these current sources

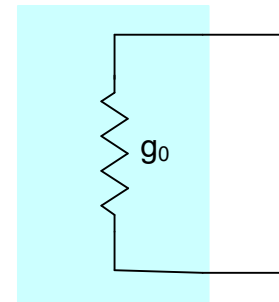
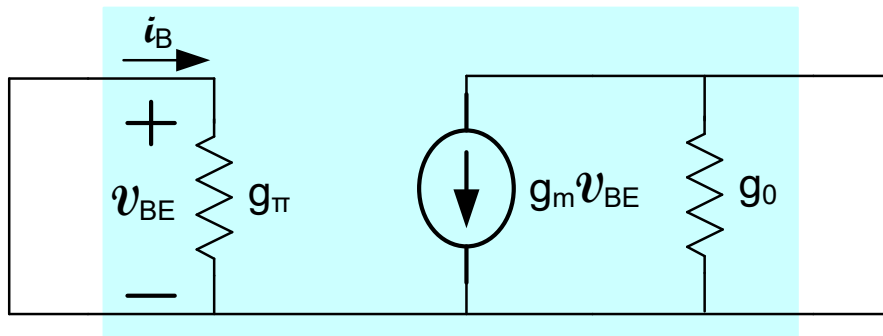


# Basic Current Sources and Sinks

## Small-signal Model of BJT Current Sinks and Sources

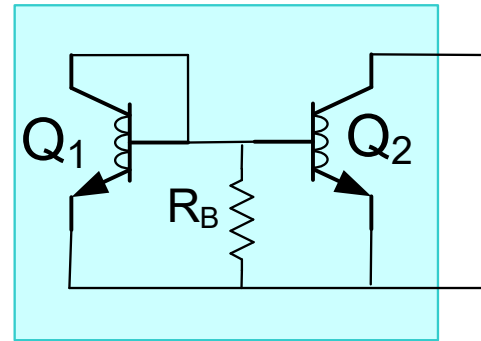
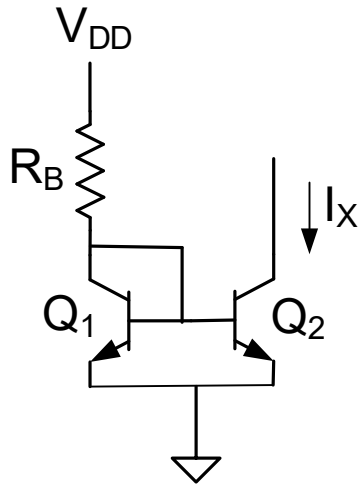


Small-signal BE-Connected  
(Not Diode Connected !)

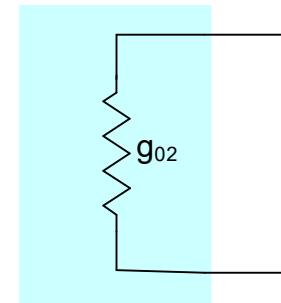
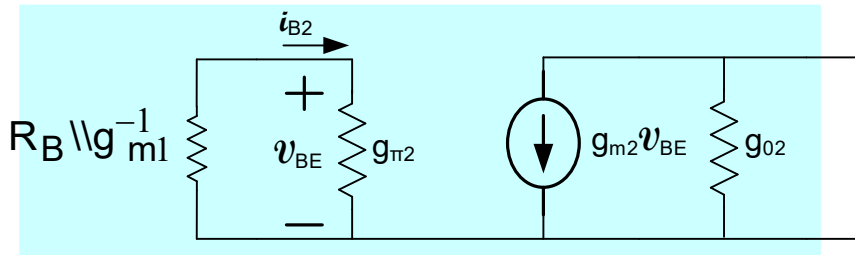


# Basic Current Sources and Sinks

## Small-signal Model of BJT Current Sinks and Sources



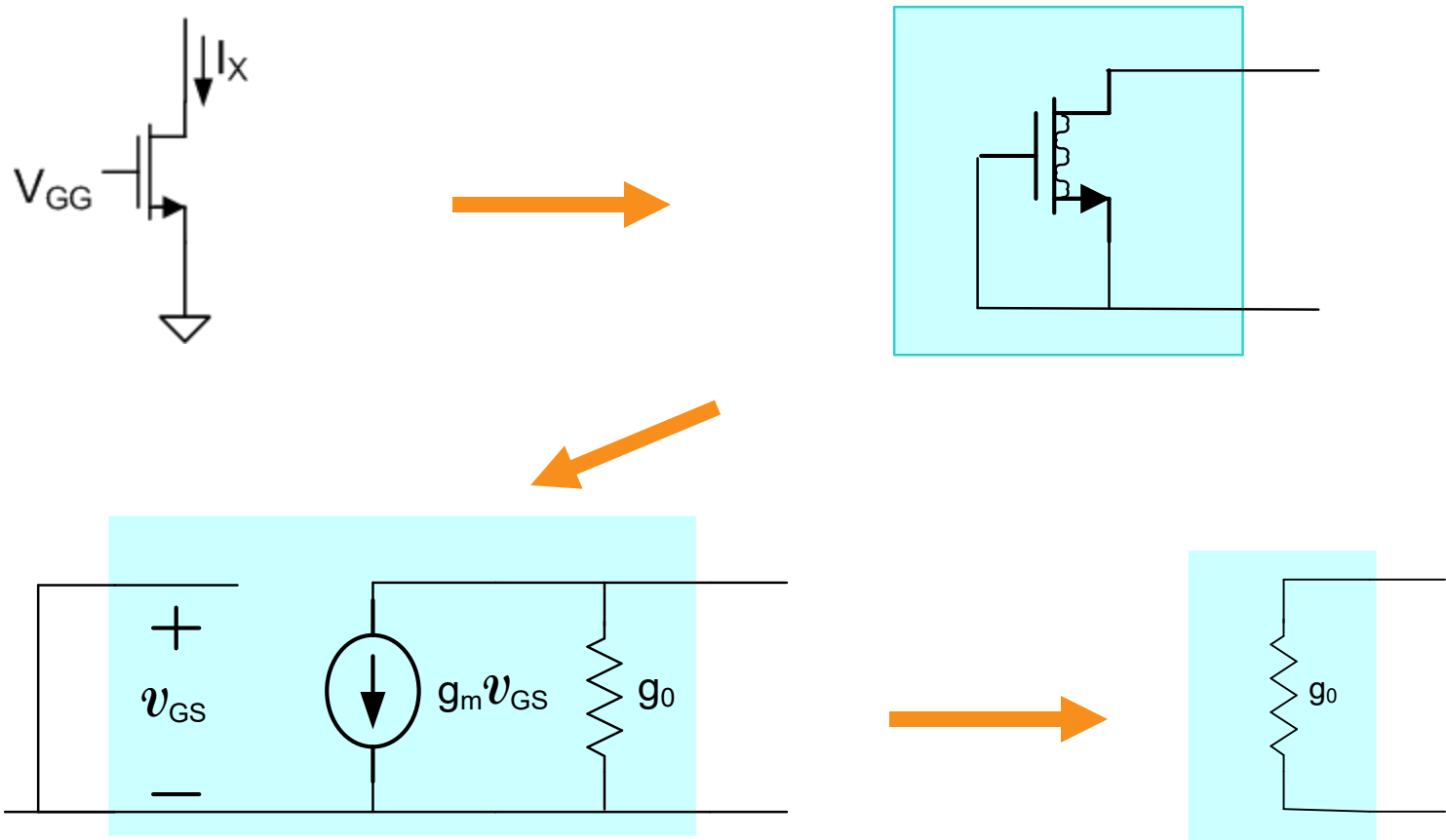
Small-signal of  $Q_1$   
Diode connected



Small-signal model of all other BJT Sinks and Sources introduced so far are the same

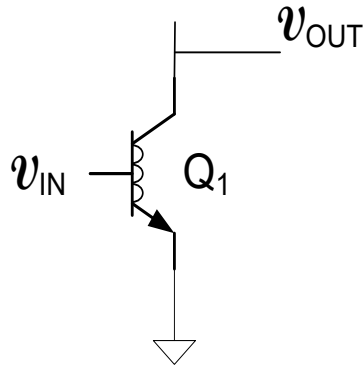
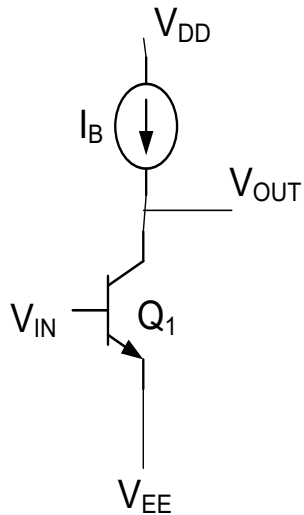
# Basic Current Sources and Sinks

## Small-signal Model of MOS Current Sinks and Sources

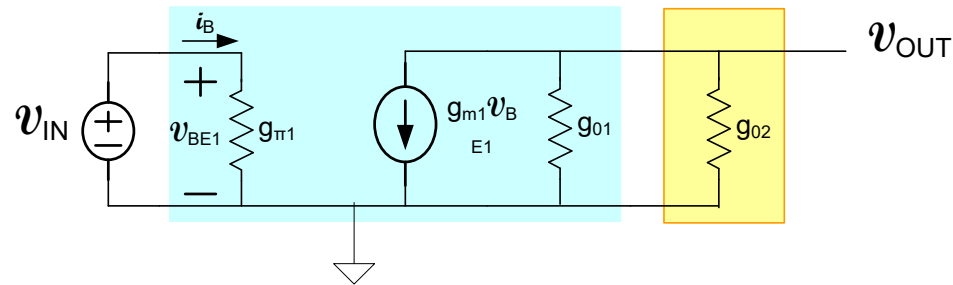
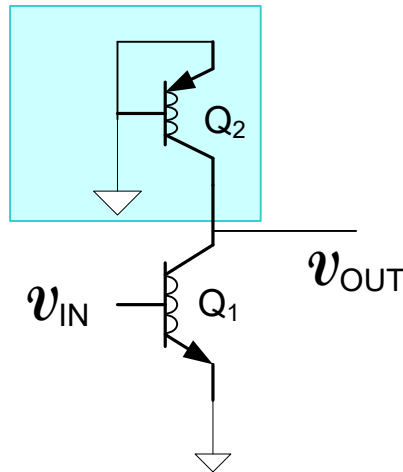
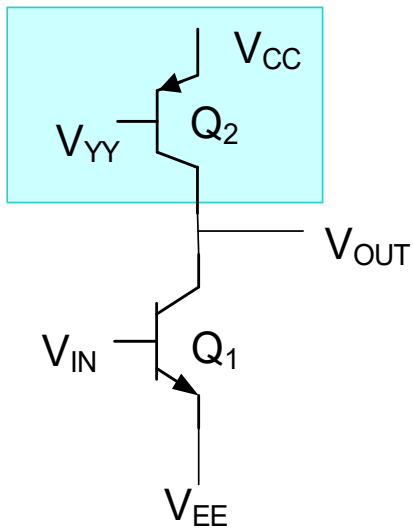


**Small-signal model of all other MOS Sinks and Sources introduced thus far are the same**

# High-gain amplifier

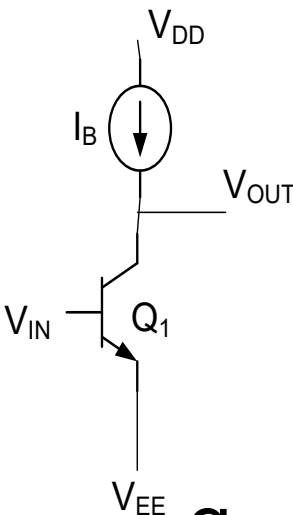


$$A_V = \frac{-g_m}{g_o}$$



$$A_V = \frac{-g_{m1}}{g_{o1} + g_{o2}} \approx \frac{-g_{m1}}{2g_{o1}}$$

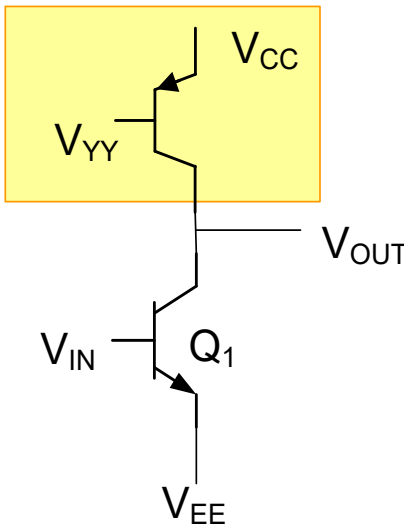
# High-gain amplifier



A circuit diagram of a common-emitter amplifier. The base of the transistor  $Q_1$  is connected to an input terminal  $V_{IN}$ . The emitter is connected to a negative supply terminal  $V_{EE}$ . The collector is connected to a positive supply terminal  $V_{DD}$  through an ideal current source  $I_B$ . The output terminal  $V_{OUT}$  is taken from the collector.

$$A_V = \frac{-g_m}{g_0} = -8000$$

$$\frac{g_m}{g_0} = \frac{g_{m1}}{g_{01}} = \frac{V_{AF}}{V_t} \cong 8000$$



A circuit diagram of a common-emitter amplifier, similar to the first one, but with a nonideal current source load. The collector is connected to a positive supply terminal  $V_{CC}$  through a current source  $I_B$  in parallel with a resistor  $V_{YY}$ . The output terminal  $V_{OUT}$  is taken from the collector.

$$A_V \cong \frac{-g_{m1}}{2g_{01}} = -4000$$

- Nonideal current source decreased the gain by a factor of 2
- But the voltage gain is still quite large (-4000)

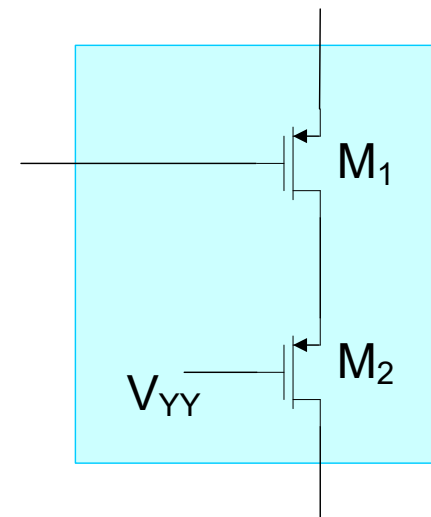
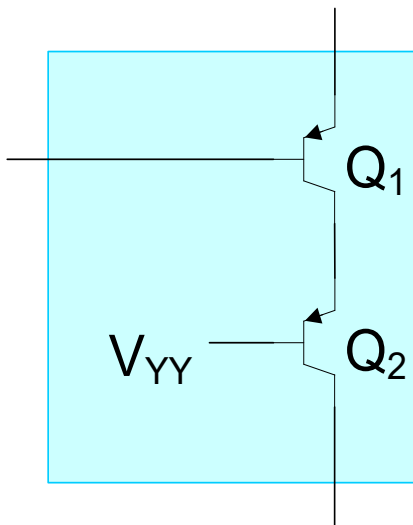
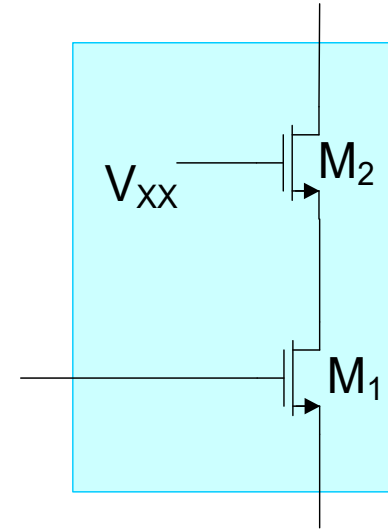
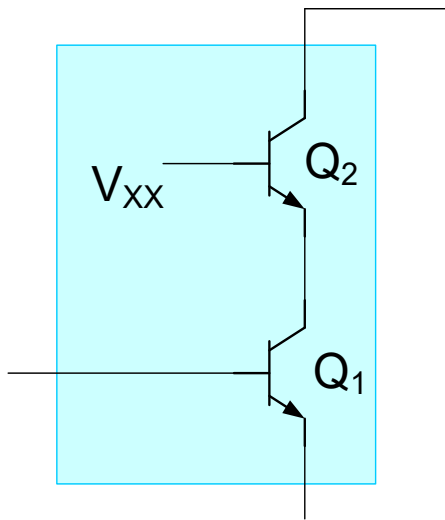
**Can the gain be made even larger?**

# High-gain amplifier

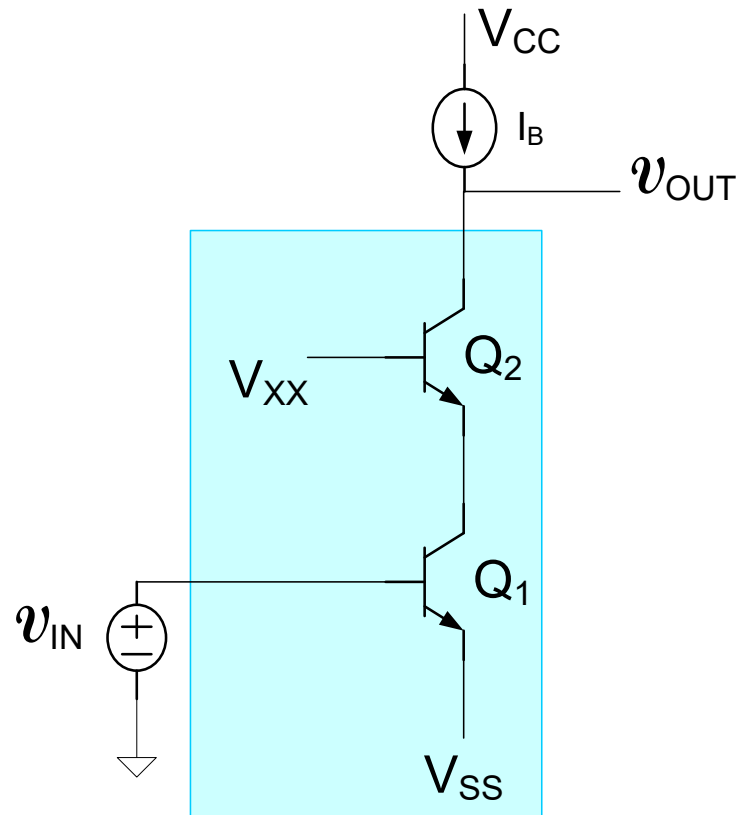
Can the gain be made even larger?

Discuss

## The Cascode Configuration



# The Cascode Amplifier (consider npn BJT version)



Discuss

- **Actually a cascade of a CE stage followed by a CB stage but usually viewed as a “single-stage” structure**
- **Cascode structure is widely used**

# Basic Amplifier Structures

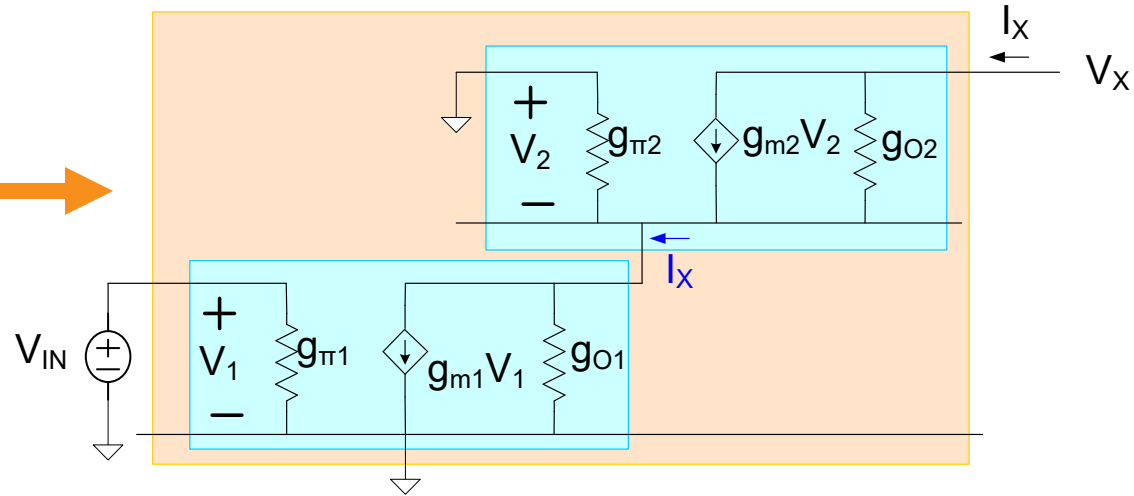
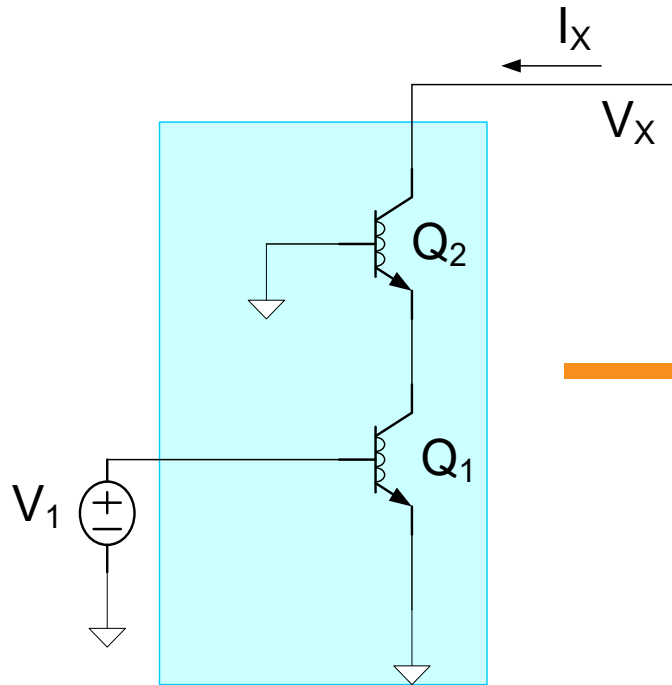
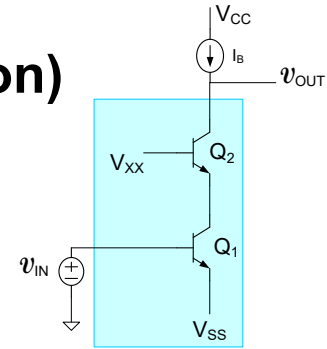
Discuss

1. Common Emitter/Common Source
2. Common Collector/Common Drain
3. Common Base/Common Gate
4. Common Emitter with  $R_E$ / Common Source with  $R_S$
- 5. Cascode (actually CE:CB or CS:CD cascade)
6. Darlington (special CE:CE or CS:CS cascade)

The first 4 are most popular

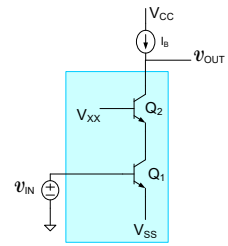


# The Cascode Amplifier (consider npn BJT version)

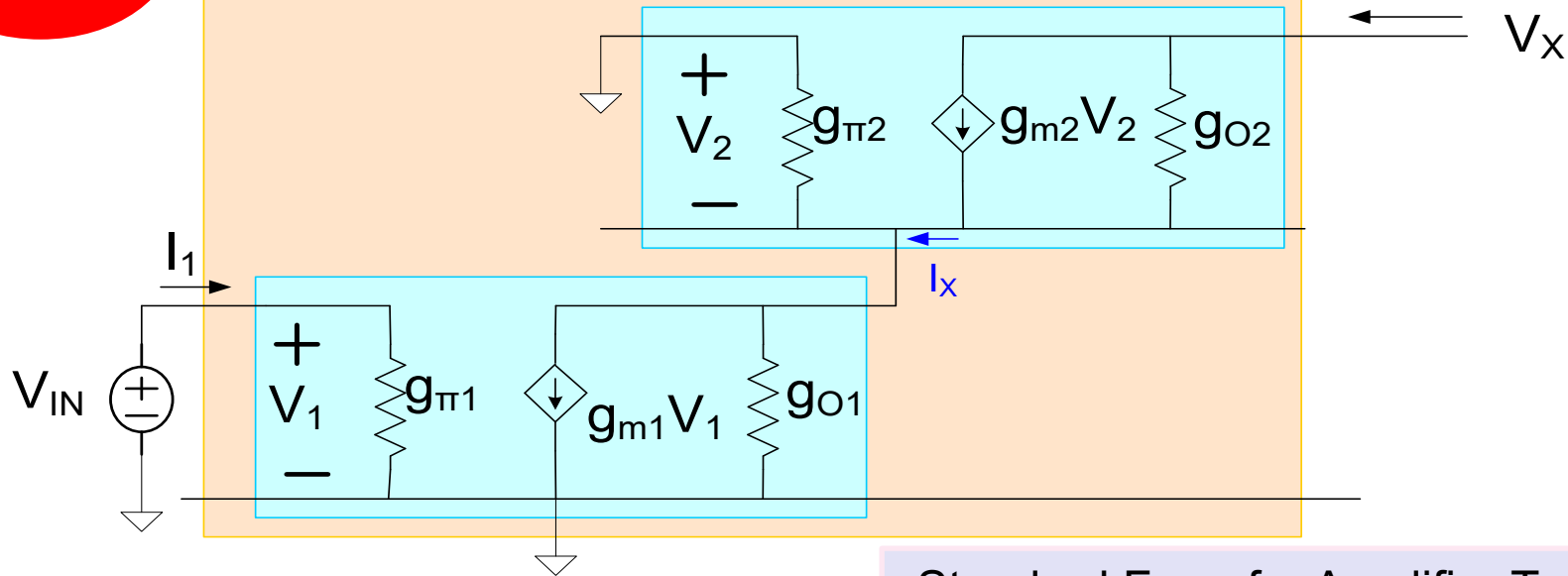


# Cascode Configuration

Discuss

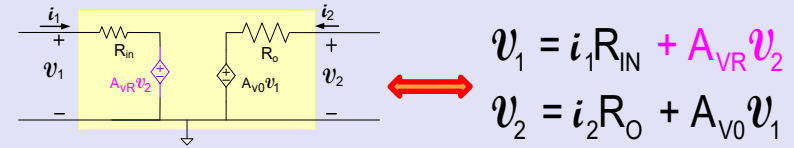


Two-port model of cascode amplifier



$$\left. \begin{aligned} (V_X + V_2)g_{o2} + V_2g_{m2} &= I_X \\ V_1g_{m1} - V_2(g_{o1} + g_{\pi2}) &= I_X \end{aligned} \right\}$$

Standard Form for Amplifier Two-Port



Observing  $V_1 = V_{IN}$  and eliminating  $V_2$  between these two equations, we obtain

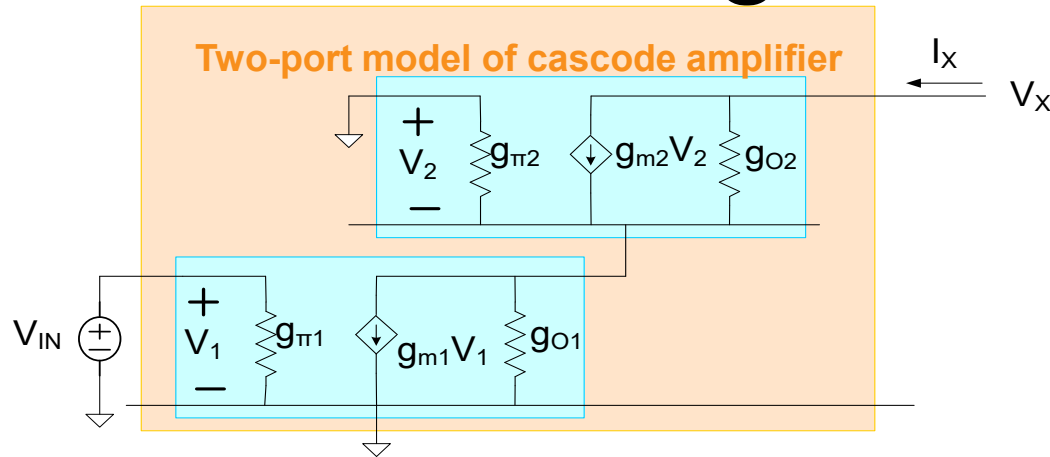
$$V_{IN} = I_1 \cdot \frac{1}{g_{\pi1}}$$

and

$$V_X = I_X \cdot \left[ \frac{g_{o1} + g_{o2} + g_{\pi2} + g_{m2}}{g_{o2}(g_{o1} + g_{\pi2})} \right] - V_{IN} \cdot \left[ \frac{g_{m1}(g_{o2} + g_{m2})}{g_{o2}(g_{\pi2} + g_{o1})} \right]$$

# Cascode Configuration

Discuss



$$V_X = I_X \cdot \left[ \frac{g_{o1} + g_{o2} + g_{\pi2} + g_{m2}}{g_{o2}(g_{o1} + g_{\pi2})} \right] - V_{IN} \cdot \left[ \frac{g_{m1}(g_{o2} + g_{m2})}{g_{o2}(g_{\pi2} + g_{o1})} \right]$$

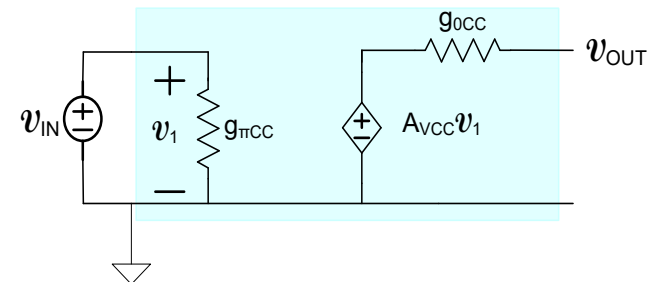
$$V_{IN} = I_1 \cdot \frac{1}{g_{\pi1}}$$

It thus follows for the npn bipolar structure that :

$$A_{VCC} = - \left[ \frac{g_{m1}(g_{o2} + g_{m2})}{g_{o2}(g_{\pi2} + g_{o1})} \right] \cong - \left[ \frac{g_{m1}g_{m2}}{g_{o2}g_{\pi2}} \right]$$

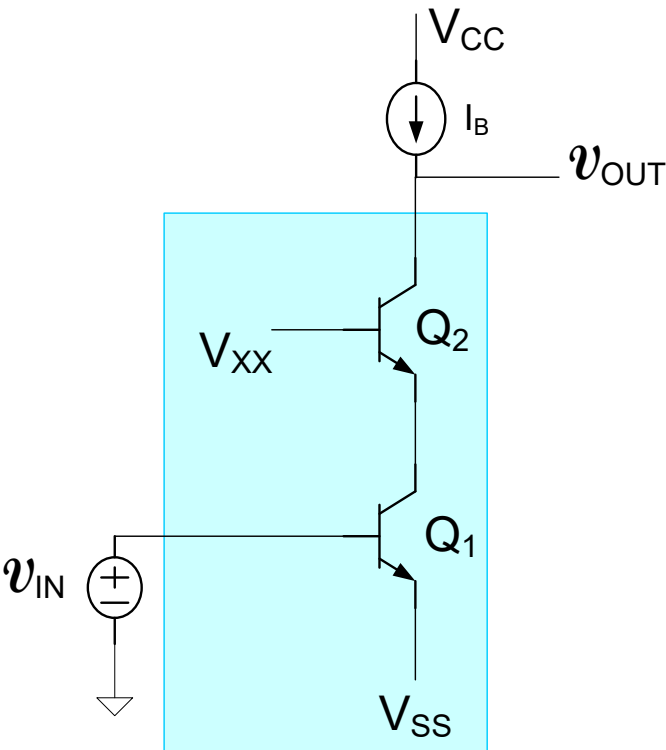
$$g_{oCC} = \left[ \frac{g_{o2}(g_{o1} + g_{\pi2})}{g_{o1} + g_{o2} + g_{\pi2} + g_{m2}} \right] \cong \left[ \frac{g_{o2}g_{\pi2}}{g_{m2}} \right]$$

$$g_{\pi CC} = g_{\pi1}$$



# Cascode Configuration

Discuss



$$A_{V_{CC}} \cong - \left[ \frac{g_{m1} g_{m2}}{g_{o2} g_{\pi 2}} \right]$$

$$g_{oCC} \cong \left[ \frac{g_{o2} g_{\pi 2}}{g_{m2}} \right]$$

$$g_{\pi CC} = g_{\pi 1}$$

---

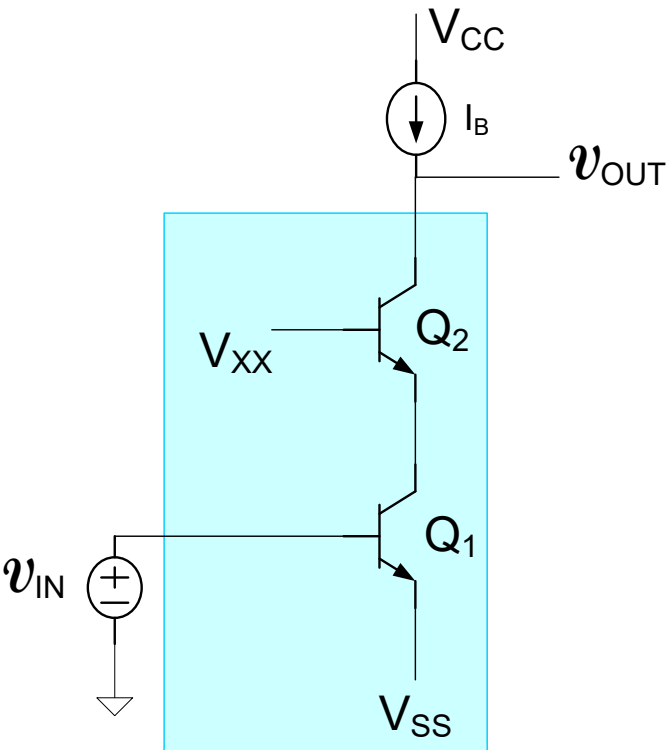

$$A_{V_{CC}} \cong - \left[ \frac{g_{m1}}{g_{o2}} \beta \right] \cong - \left[ \frac{g_{m1}}{g_{o1}} \right] \beta$$

$$g_{oCC} \cong \frac{g_{o1}}{\beta}$$

- Voltage gain is a factor of  $\beta$  larger than that of the CE amplifier with current source load
- Output impedance is a factor of  $\beta$  larger than that of the CE amplifier

# Cascode Configuration

Discuss



$$A_{V_{CC}} \cong - \left[ \frac{g_{m1} \beta}{g_{o2}} \right] \cong - \left[ \frac{g_{m1}}{g_{o1}} \right] \beta$$

$$g_{o_{CC}} \cong \frac{g_{o2}}{\beta}$$

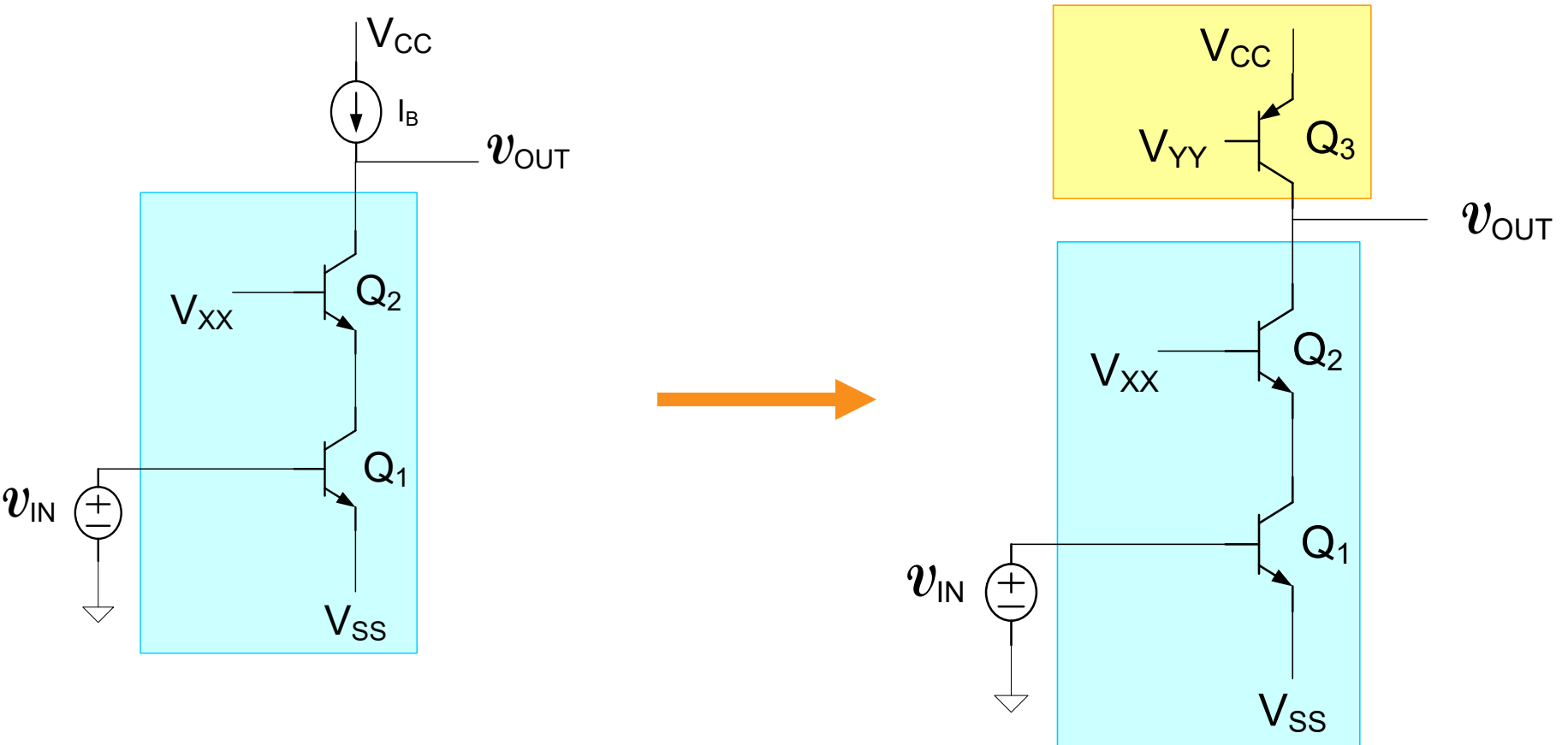
$$A_{V_{CC}} \cong - \left[ \frac{g_{m1}}{g_{o1}} \right] \beta = \left[ \frac{2V_{AF}}{V_t} \right] \beta = [-8000]100$$

$$A_{V_{CC}} \cong -800,000$$

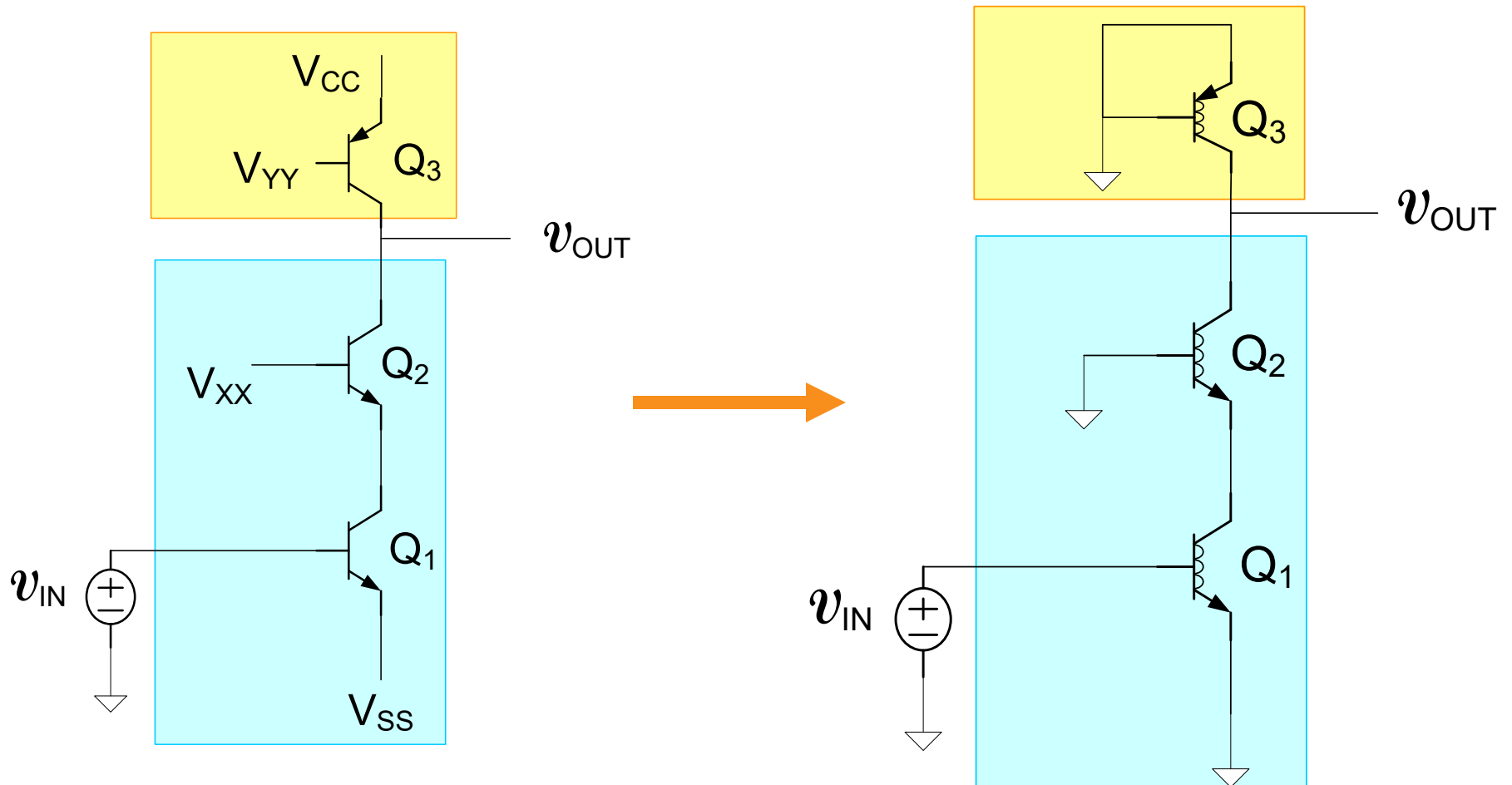
**This gain is very large and only requires two transistors!**

**What happens to the gain if a transistor-level current source is used for  $I_B$ ?**

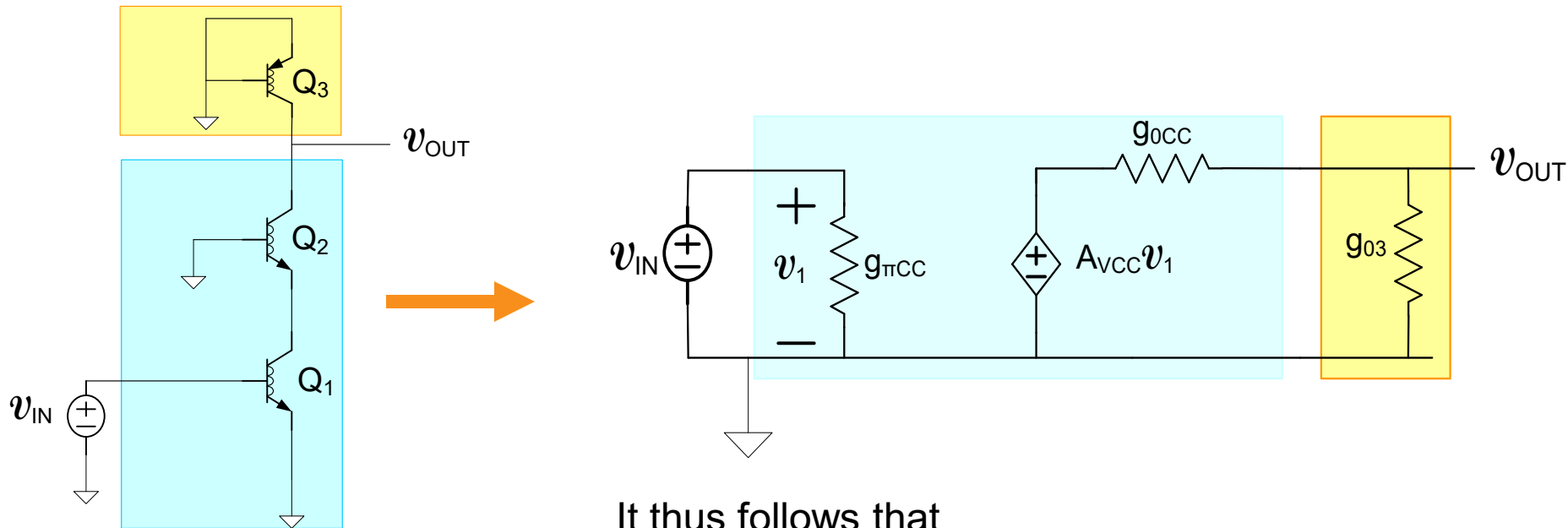
# Cascode Configuration



# Cascode Configuration



# High-gain amplifier comparisons



It thus follows that

$$A_V = A_{VCC} \left[ \frac{g_{0CC}}{g_{03} + g_{0CC}} \right]$$

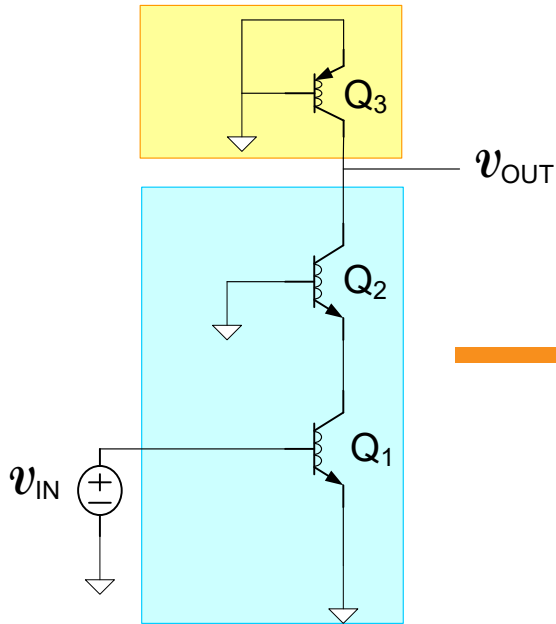
But  $g_{0CC} \simeq g_{01}/\beta = g_{03}/\beta$

$$A_V \simeq A_{VCC} \left[ \frac{g_{0CC}}{g_{03}} \right] \simeq \frac{A_{VCC}}{\beta}$$

**This is a dramatic reduction in gain compared to what the ideal current source biasing provided**



# Cascode Configuration



$$A_V \cong A_{VCC} \left[ \frac{g_{0CC}}{g_{03}} \right] \cong \frac{A_{VCC}}{\beta}$$

But recall

$$A_{VCC} \cong - \left[ \frac{g_{m1}}{g_{01}} \right] \beta$$

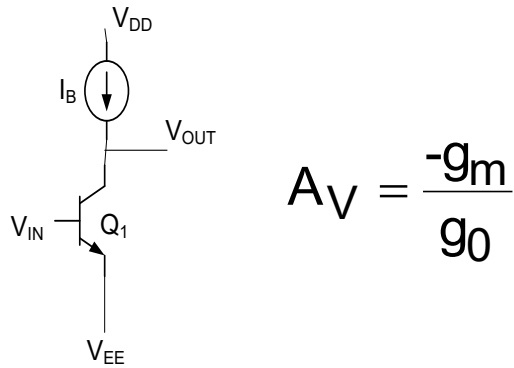
Thus

$$A_V \cong - \left[ \frac{g_{m1}}{g_{01}} \right]$$

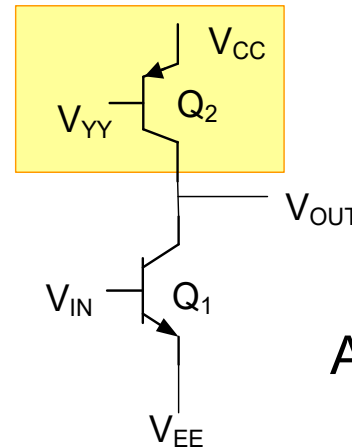
$$A_V \cong - \left[ \frac{I_{CQ} / V_t}{I_{CQ} / V_{AF}} \right] = - \left[ \frac{V_{AF}}{V_t} \right] \cong -8000$$

- This is still a factor of 2 better than that of the CE amplifier with transistor current source  $\left( A_{VCE} \cong - \left[ \frac{g_{m1}}{2g_{01}} \right] \right)$
- It only requires one additional transistor
- But its not nearly as good as the gain the cascode circuit seemed to provide

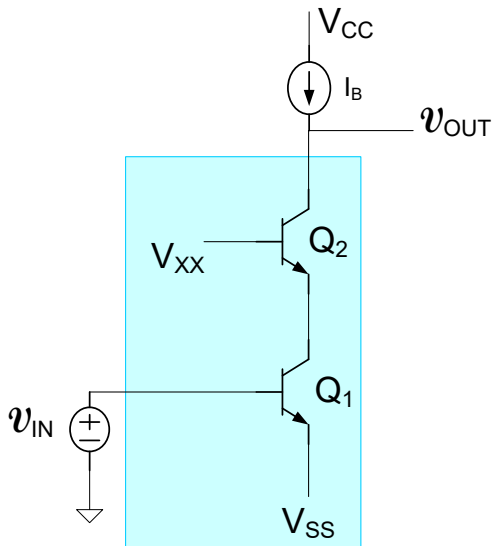
# Cascode Configuration Comparisons



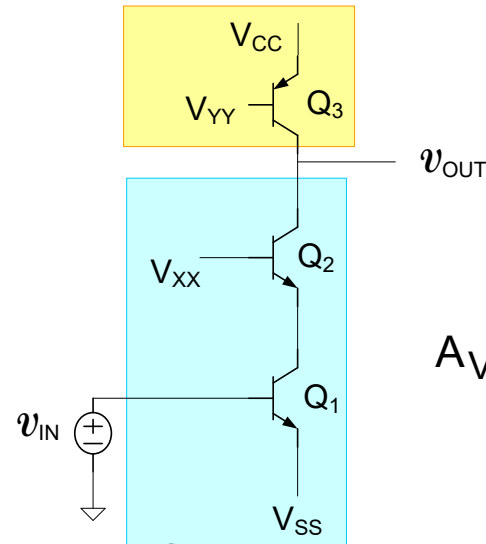
$$A_V = \frac{-g_m}{g_0}$$



$$A_V \cong \frac{-g_{m1}}{g_{01} + g_{02}} = \frac{-g_{m1}}{2g_{01}}$$



$$A_V \cong - \left[ \frac{g_{m1}}{g_{01}} \right] \beta$$



$$A_V \cong - \left[ \frac{g_{m1}}{\frac{g_{01}}{\beta} + g_{03}} \right] \cong - \left[ \frac{g_{m1}}{g_{03}} \right]$$

**Gain limited by output impedance of current source !!**

**Can we design a better current source?**

**In particular, one with a higher output impedance?**

# Better current sources

Need a higher output impedance than  $g_o$

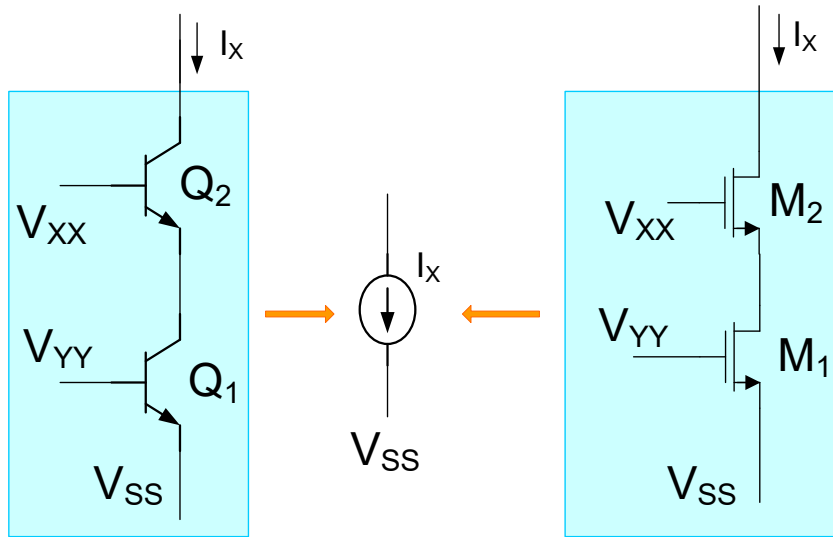


The output impedance of the cascode circuit itself was very large !

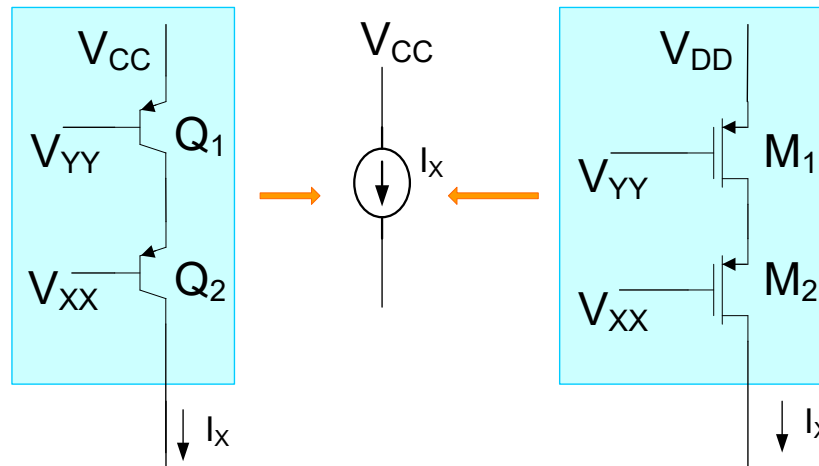
$$g_{oCC} \approx \frac{g_{o1}}{\beta}$$

Can a current source be built with the cascode circuit ?

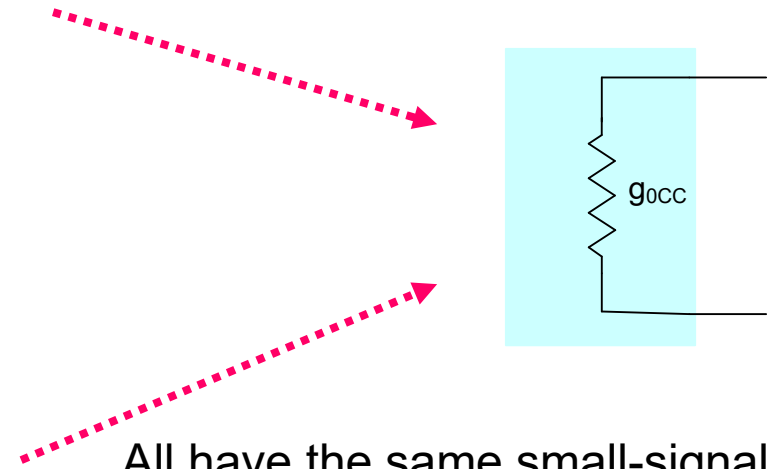
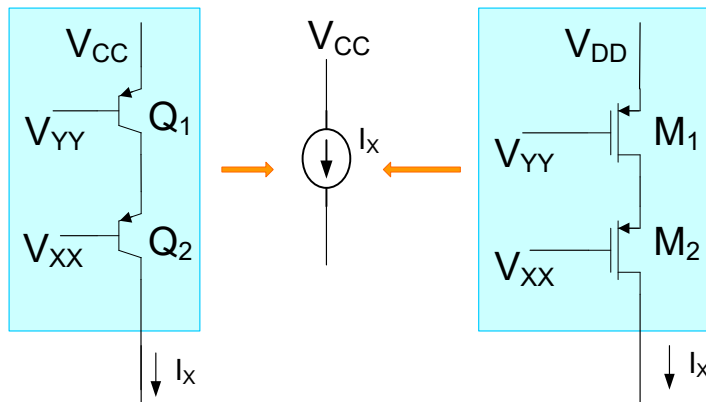
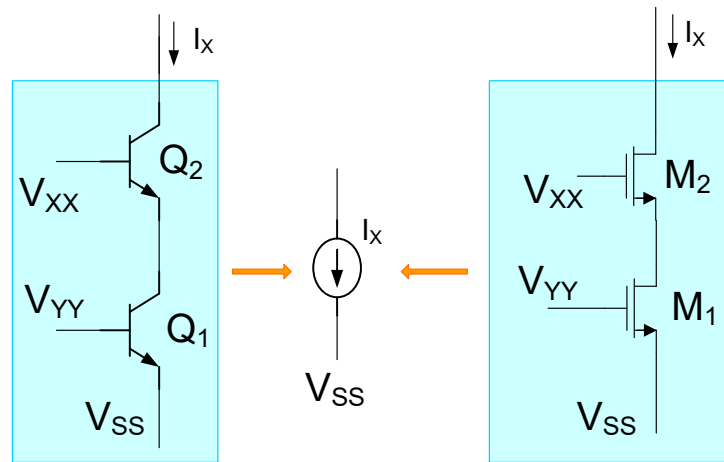
# Cascode current sources



**Discuss**



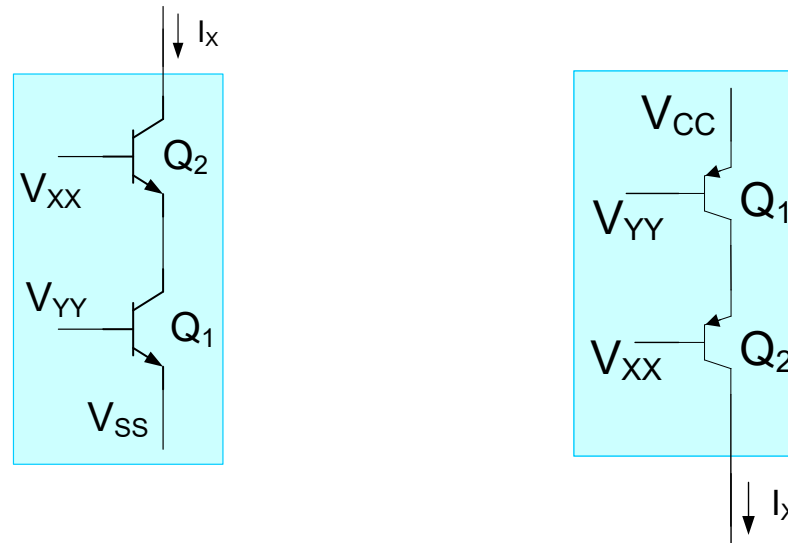
# Cascode current sources



All have the same small-signal model

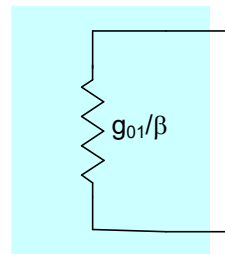
$$g_{0CC} = \left[ \frac{g_{02} (g_{01} + g_{\pi 2})}{g_{01} + g_{02} + g_{\pi 2} + g_{m2}} \right]$$

# Cascode current sources

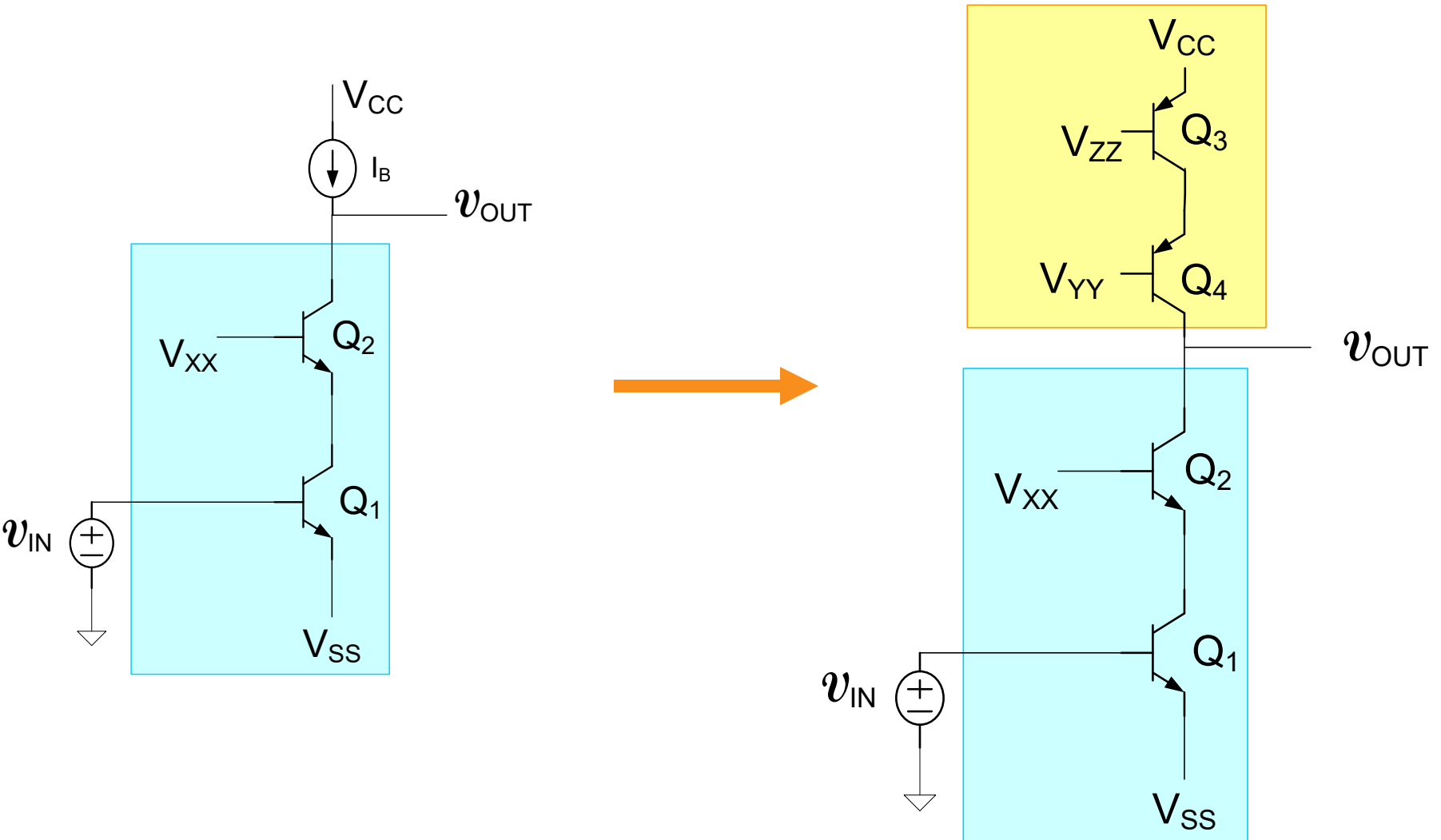


**For the BJT cascode current sources**

$$g_{oCC} = \left[ \frac{g_{o2}(g_{o1} + g_{\pi 2})}{g_{o1} + g_{o2} + g_{\pi 2} + g_{m2}} \right] \cong \left[ \frac{g_{o2}g_{\pi 2}}{g_{m2}} \right] = \frac{g_{o1}}{\beta}$$

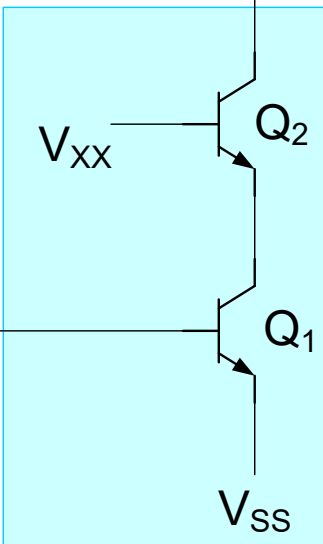
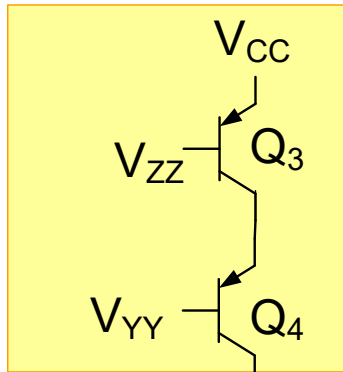


# Cascode Configuration



# Cascode Configuration

Discuss



$$A_V \cong - \left[ \frac{g_{m1}}{\frac{g_{o1}}{\beta_1} + g_{oCC}} \right] \cong - \left[ \frac{g_{m1}}{\frac{g_{o1}}{\beta_1} + \frac{g_{o3}}{\beta_3}} \right]$$

If  $\beta_1 = \beta_3 = \beta$

$$A_V = - \left[ \frac{g_{m1}}{g_{o1}} \right] \frac{\beta}{2}$$

$$A_V = - [8000] \frac{100}{2} \cong -400,000$$

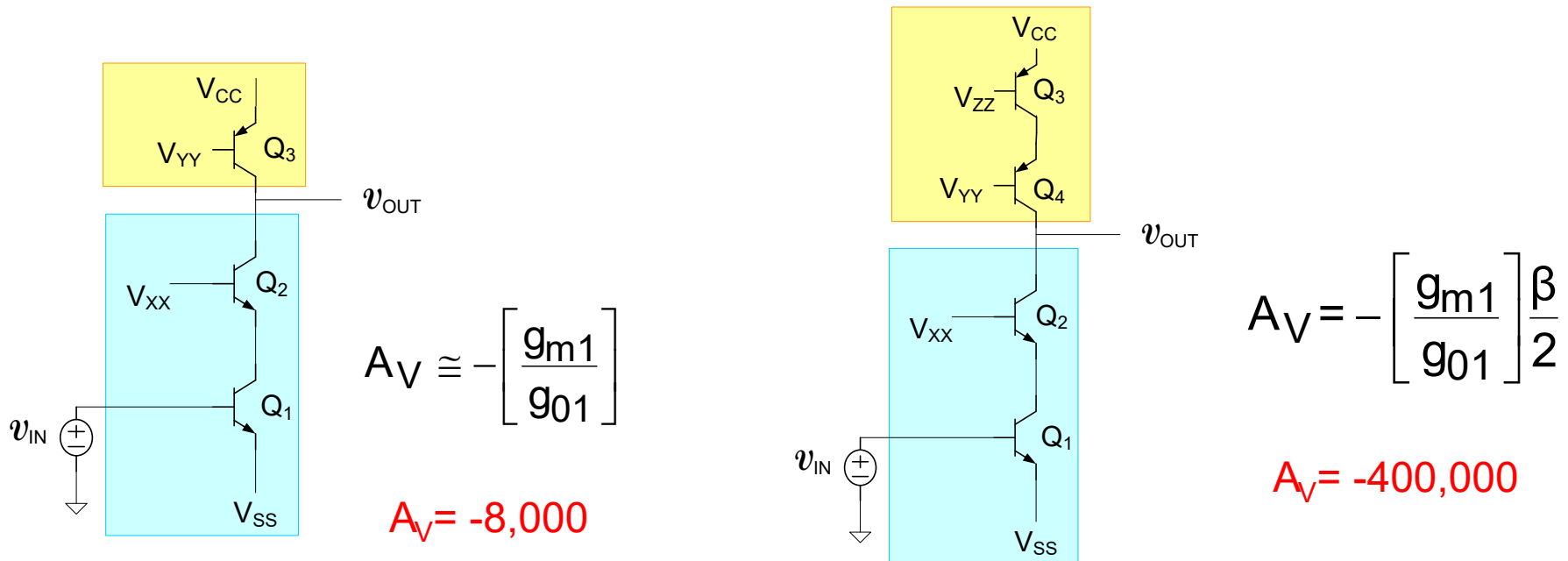
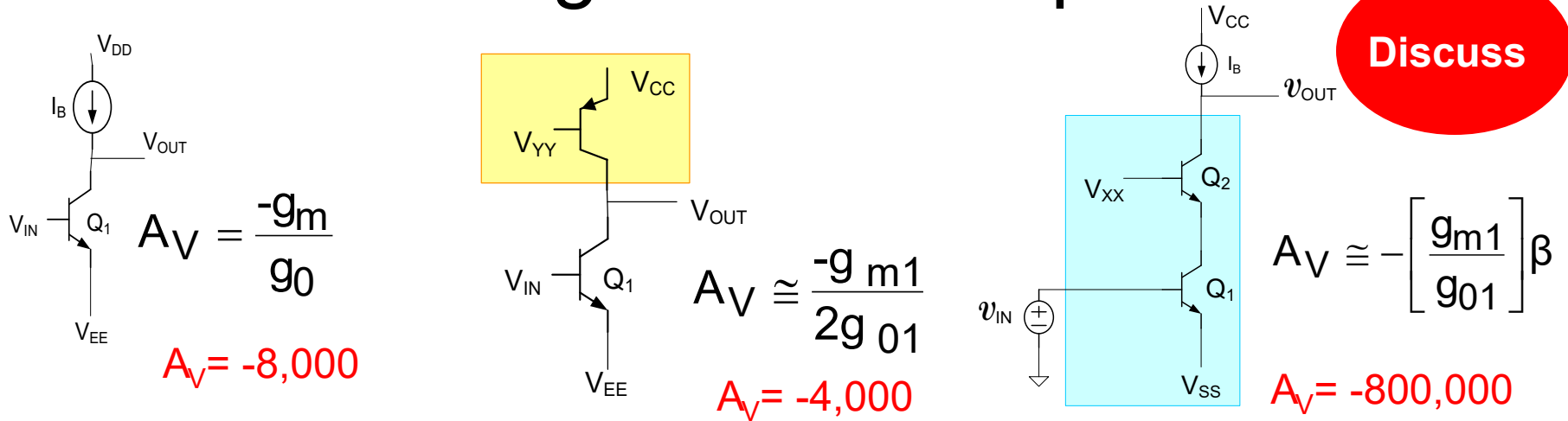
- This gain is very large and is a factor of 2 below that obtained with an ideal current source biasing
- Although the factor of 2 is not desired, the performance of this circuit is still very good
- This factor of 2 gain reduction is that same as was observed for the CE amplifier when a transistor-level current source was used
- Biasing voltages  $V_{ZZ}$  and  $V_{SS}$  are critical so seldom used single-ended but good biasing strategies exist for differential operation

$v_{IN}$

$v_{OUT}$

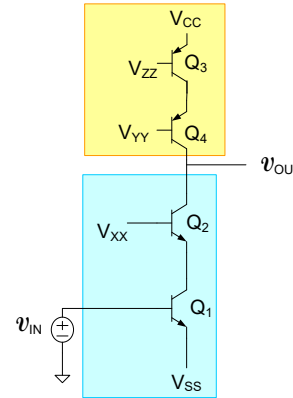
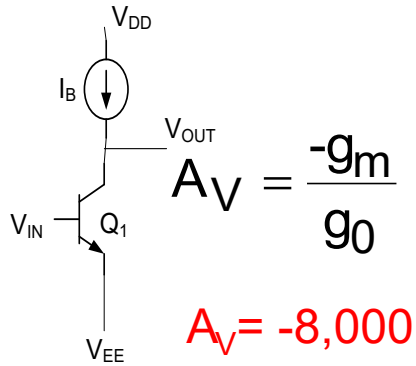


# Cascode Configuration Comparisons



Can we use more cascoding to further increase the gain?

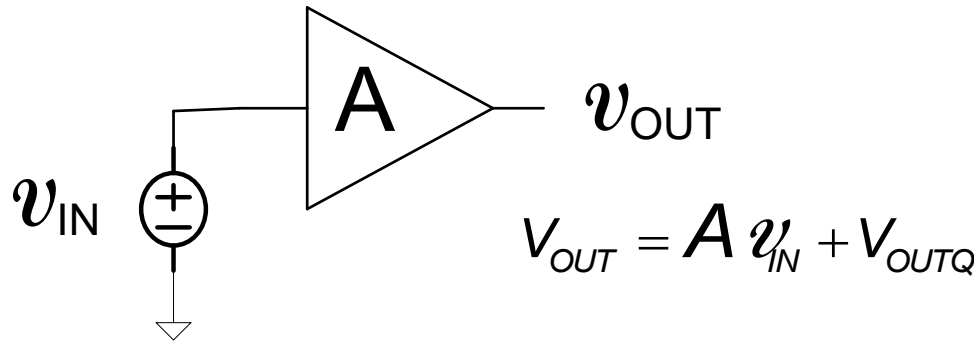
# High Gain Amplifiers Seldom Used Open Loop



$$A_V = - \left[ \frac{g_{m1}}{g_{o1}} \right] \frac{\beta}{2}$$

$A_V = -400,000$

**Discuss**

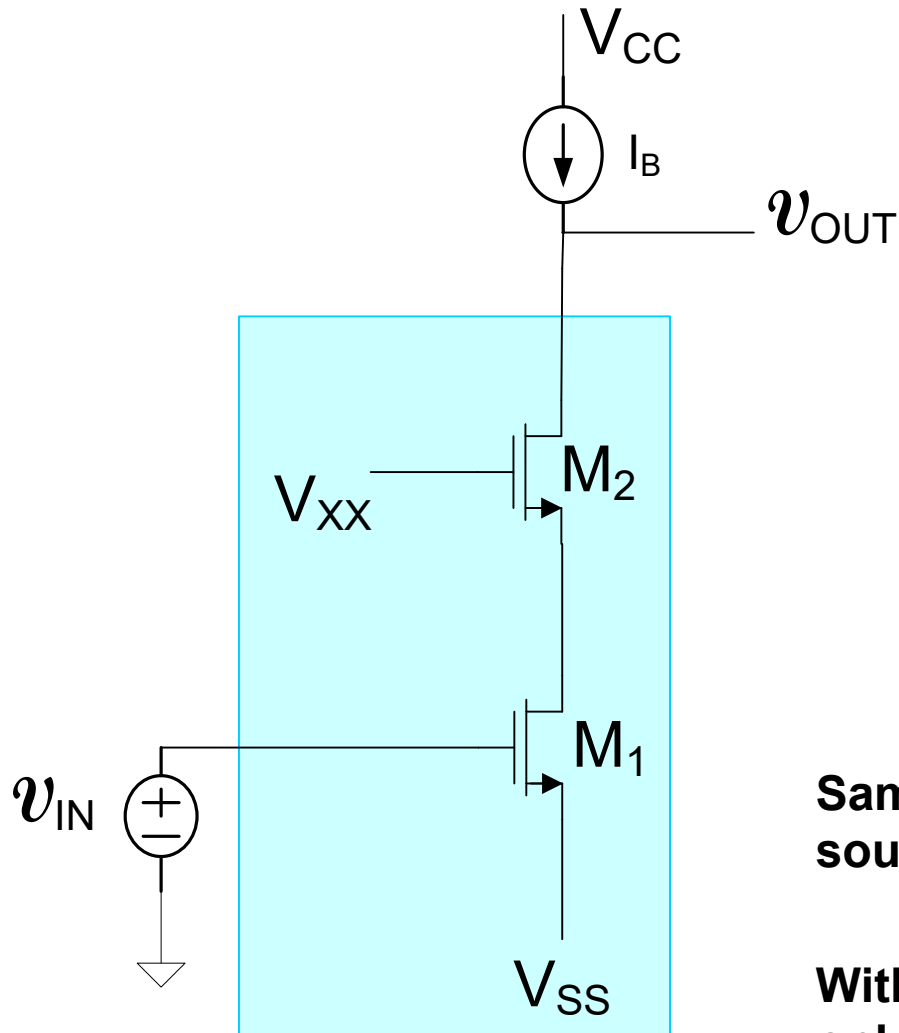


If  $A_V = -400,000$  and  $v_{IN}$  increases by 1mV, what would happen at the output?

$v_{OUT}$  would decrease by  $400,000 \times 1\text{mV} = -400\text{V}$

# The Cascode Amplifier (consider n-ch MOS version)

Discuss



$$A_{V_{CC}} \cong - \left[ \frac{g_{m1} g_{m2}}{g_{o1} g_{o2}} \right]$$

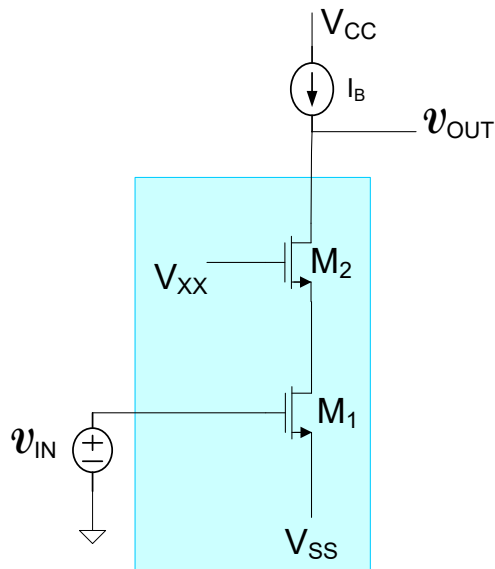
$$g_{o_{CC}} \cong \left[ \frac{g_{o1} g_{o2}}{g_{m2}} \right]$$

Same issues for biasing with current source as for BJT case

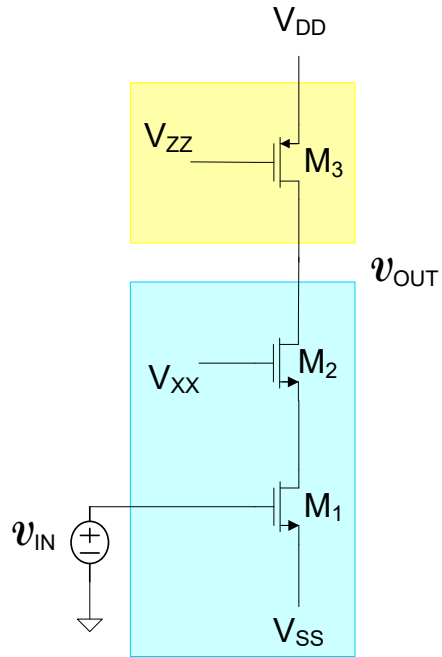
With cascode current source for  $I_B$ , gain only drops by a factor of 2 from value with ideal current source

# The Cascode Amplifier (consider n-ch MOS version)

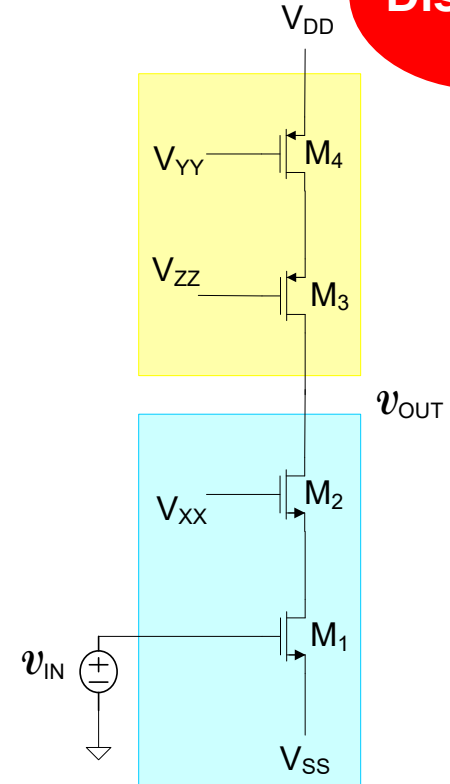
Discuss



$$A_{VCC} \cong - \left[ \frac{g_{m1} g_{m2}}{g_{o1} g_{o2}} \right]$$



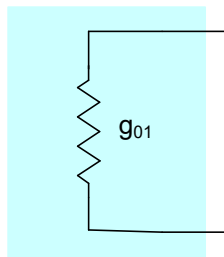
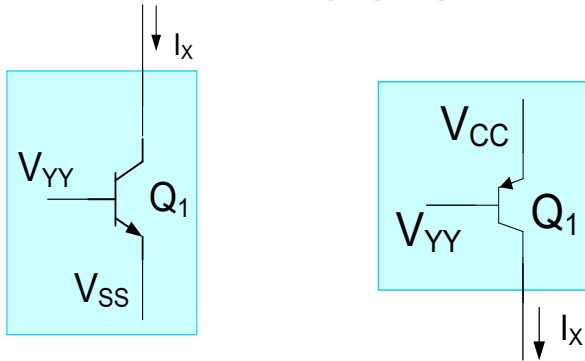
$$A_{VCC} \cong - \left[ \frac{g_{m1}}{g_{o1}} \right]$$



$$A_{VCC} \cong - \frac{1}{2} \left[ \frac{g_{m1} g_{m2}}{g_{o1} g_{o2}} \right]$$

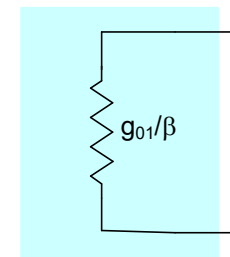
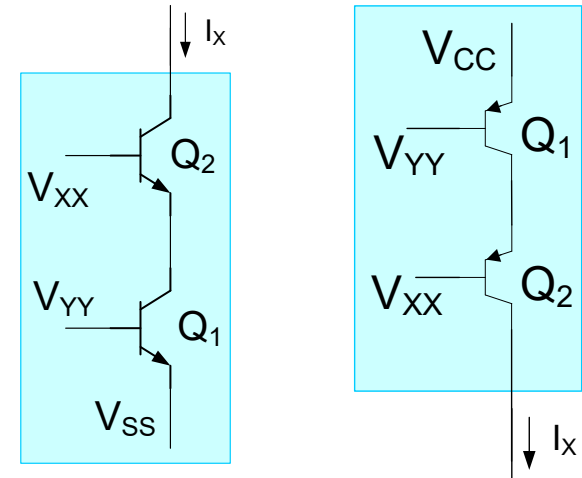
# Current Source Summary (BJT)

## Basic

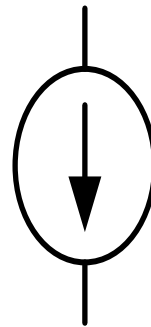


$$g_0 \cong g_{01}$$

## Cascode

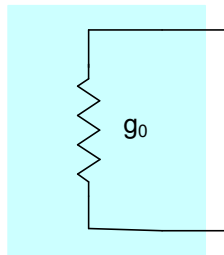
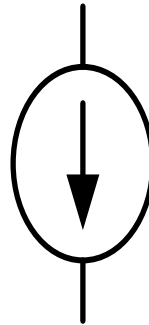
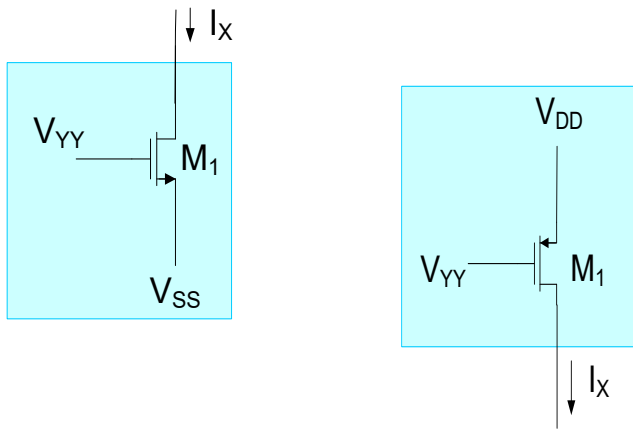


$$g_{0CC} \cong \frac{g_{01}}{\beta}$$



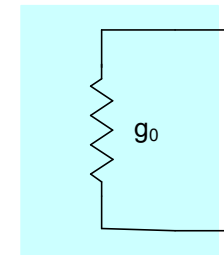
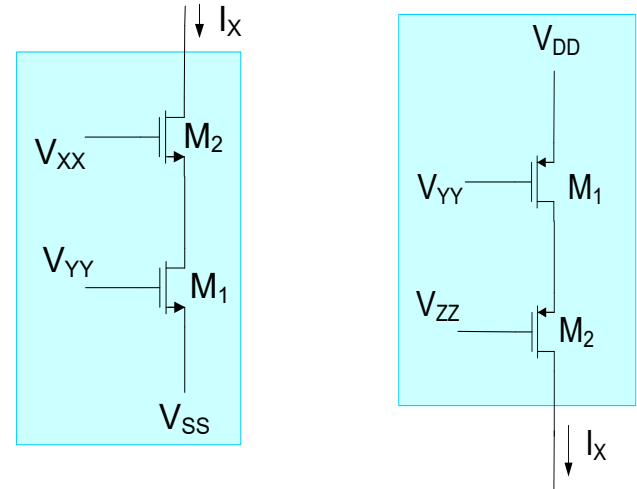
# Current Source Summary (MOS)

## Basic



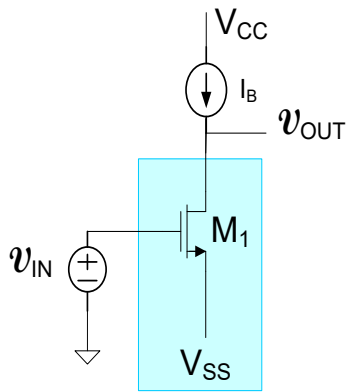
$$g_0 \cong g_{01}$$

## Cascode

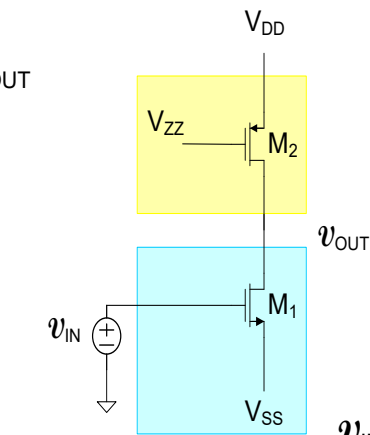


$$g_0 \cong g_{01} \frac{g_{02}}{g_{m2}}$$

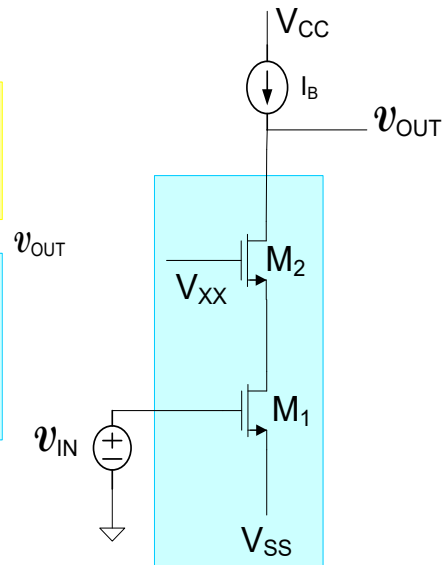
# High Gain Amplifier Comparisons ( n-ch MOS)



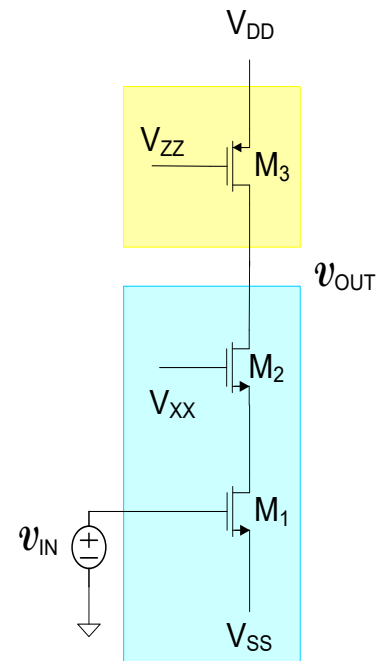
$$A_V \cong - \left[ \frac{g_{m1}}{g_{o1}} \right]$$



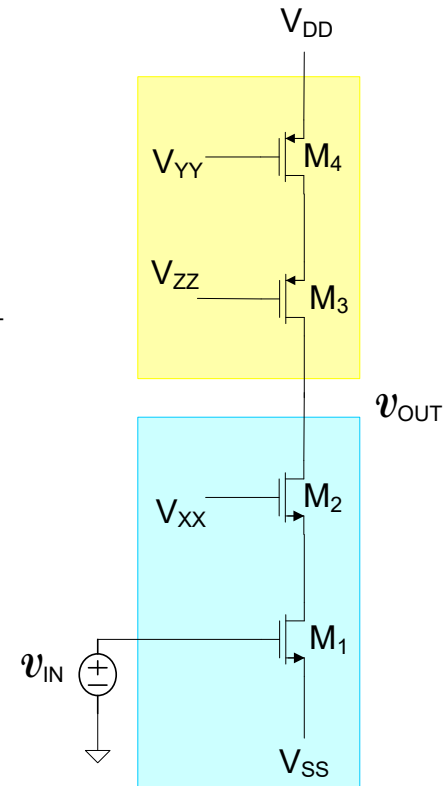
$$A_V \cong - \frac{1}{2} \left[ \frac{g_{m1}}{g_{o1}} \right]$$



$$A_{VCC} \cong - \left[ \frac{g_{m1}g_{m2}}{g_{o1}g_{o2}} \right]$$

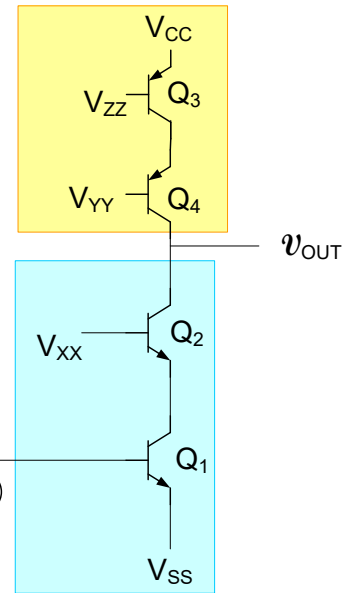
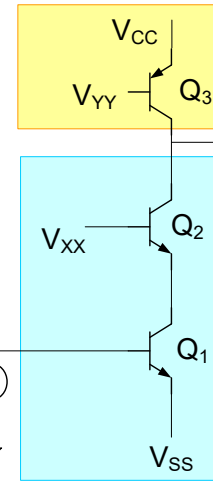
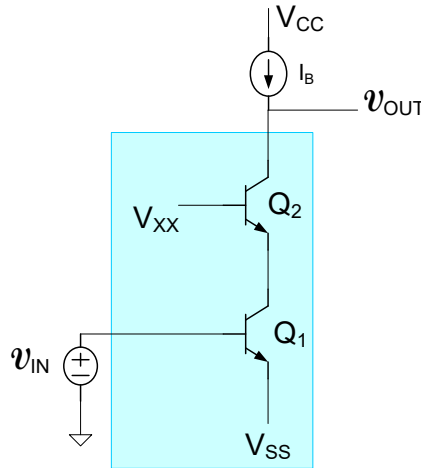
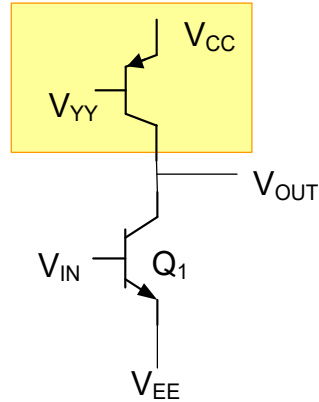
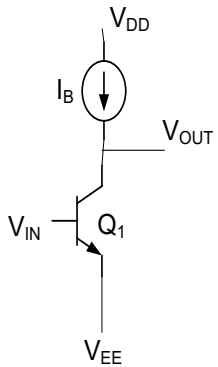


$$A_{VCC} \cong - \left[ \frac{g_{m1}}{g_{o1}} \right]$$



$$A_{VCC} \cong - \frac{1}{2} \left[ \frac{g_{m1}g_{m2}}{g_{o1}g_{o2}} \right]$$

# High Gain Amplifier Comparisons (BJT)



$$A_V = \frac{-g_m}{g_0}$$

$$A_V \cong -\frac{1}{2} \frac{g_{m1}}{g_{01}}$$

$$A_V \cong -\left[ \frac{g_{m1}}{g_{01}} \right] \beta$$

$$A_V \cong -\left[ \frac{g_{m1}}{g_{01}} \right]$$

$$A_V = -\left[ \frac{g_{m1}}{g_{01}} \right] \frac{\beta}{2}$$

- Single-ended high-gain amplifiers inherently difficult to bias (because of the high gain)
- Biasing becomes practical when used in differential applications
- These structures are widely used but usually with differential inputs





Stay Safe and Stay Healthy !

End of Lecture 34